# MSK5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK581) Updated on December 2 March 21, 2009 (MSK5822F March 26, 2009 (MSK5810F September 3, 2009 (MSK5810F November 6, 2009 (MSK5810F May 14, 2010 (MSK5810FF September 17, 2010 (MSK5810FF December 10, 2010 (MSK5810FF April 1, 2011 (MSK5810FF	24, 2008 $RH - 1^{st}$ Test) $RH - 2^{nd}$ Test) $DRH - 3^{rd}$ Test) $DRH - 4^{th}$ Test) $H - 5^{th}$ Test) $ORH - 6^{th}$ Test) $ORH - 7^{th}$ Test) $I - 8^{th}$ Test)
July 8, 2011 (MSK5810RH	
June 14, 2013 (MSK5810RH – 10 <sup>th</sup> Test,	
	Transistor Wafer Lot: CJ302831#13)
June 14, 2013 (MSK5810RH – 11 <sup>th</sup> Test,	IC Wafer Lot: WD0051441#9
	Transistor Wafer Lot: CJ302831#21)
November 6, 2013 (MSK5810RH – 12 <sup>th</sup> Test,	IC Wafer Lot: W10809524.1 #8
	Transistor Wafer Lot: CJ302831RC#20)
August 28, 2015 (MSK5810RH – 13 <sup>th</sup> Test,	IC Wafer Lot: WP005144.1
<b>3 1 1</b>	Transistor Wafer Lot: P741F1002 #21)
November 8, 2016 (MSK5810RH – 14 <sup>th</sup> Test,	IC Wafer Lot: WP005144.1 #9
	Transistor Wafer Lot: PF01F1005 #6)
March 29, 2017 (MSK5810RH – 15 <sup>th</sup> Test,	IC Wafer Lot: WP005144.1 #8
	Transistor Wafer Lot: PF01F1005 #6)
September 15, 2017 (MSK5810RH – 16 <sup>th</sup> Test,	IC Wafer Lot: W10809524.1 #8
	Transistor Wafer Lot: DL153631 #3)
January 12, 2018 (MSK5810RH – 17 <sup>th</sup> Test,	IC Wafer Lot: WP005144.1 #8
5anuary 12, 2010 (monorton 11 - 17) rest,	
August 22, 2010 (MCKE010DLL, 10th Tast	Transistor Wafer Lot: P741F1002 #21)
August 22, 2018 (MSK5810RH – 18 <sup>th</sup> Test,	IC Wafer Lot: WP005144.1 #8
	Transistor Wafer Lot: PG31F100K Wf#17)

N. Kresse J. Joy

Anaren, Inc. – MSK Products

The total dose radiation test plan for the MSK5810RH series was developed to qualify the devices as Radiation Hardened to 300 Krad(Si). The testing was performed beyond 300 Krad(Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK5810RH.

### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a Cobalt 60 radiation source. The dose rate was determined to be 117.4 Rad(Si)/sec. The total dose schedule can be found in Table I.

# III. <u>Test Setup</u>:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 160 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation, the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as one control device, at each total dose level. All electrical tests were completed within one hour of irradiation. Each subsequent dose was performed within two hours of the previous irradiation.

### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting Anaren Inc. – MSK Products.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing and statistical analysis, Feedback Voltage, Shutdown Threshold, Shutdown Hysteresis and Output Current Limit exhibited shift due to irradiation, however all performance curves stayed within specification beyond 300 Krad(Si) TID.

MSK5810RH Biased/Unbiased Dose Rate Schedule

Dosimetry Equipme	ent
Bruker Biospin # 01	62

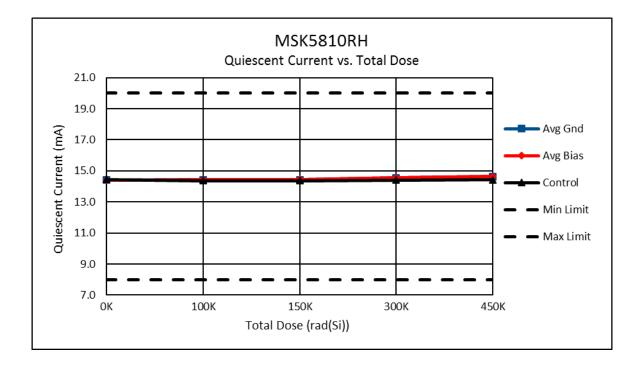
Irradiation Date
8/22/18

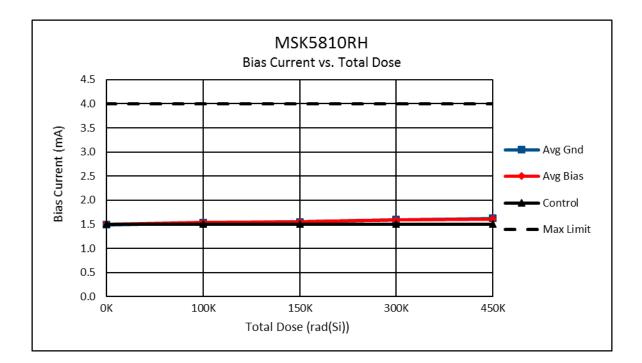
Exposure Length (min:sec)		Cumulative Dose rads(Si)
14:37	103,00	103,000
7:19	51,500	154,500
21:56	154,500	309,000
21:56	154,500	463,500

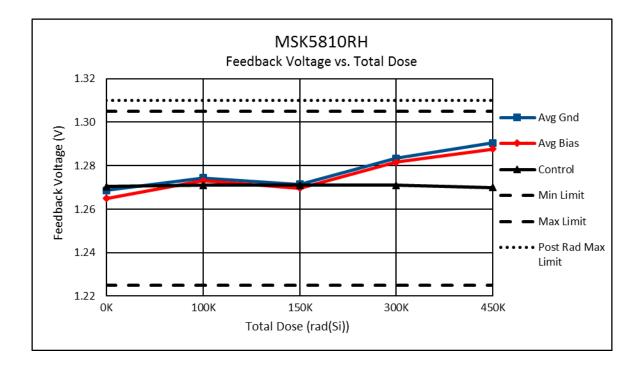
Biased S/N – 0027, 0028, 0029, 0030, 00	)31
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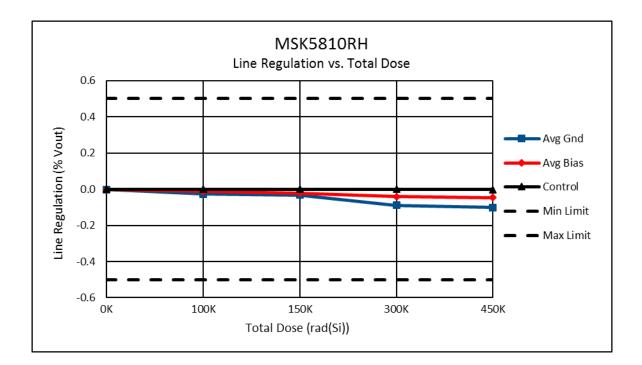
Unbiased S/N –	0032	0033	0034	0035 0036	
	0002,	00000,	000-,	0000, 0000	

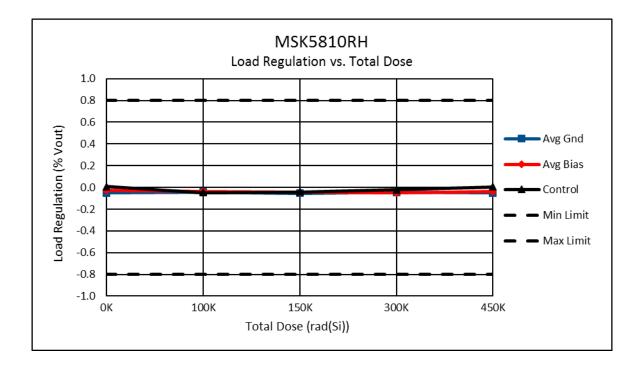
Table 1

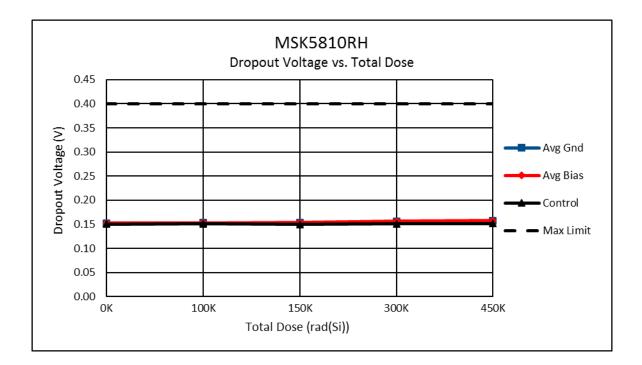


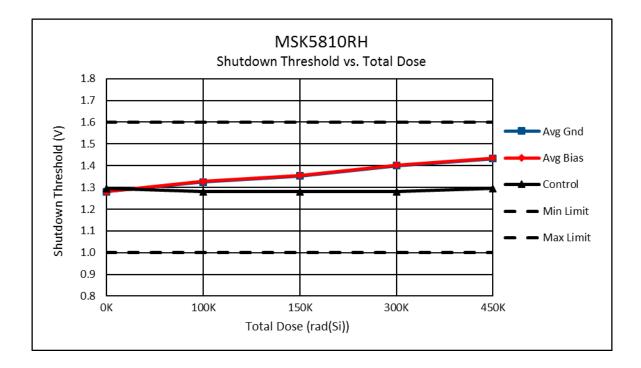


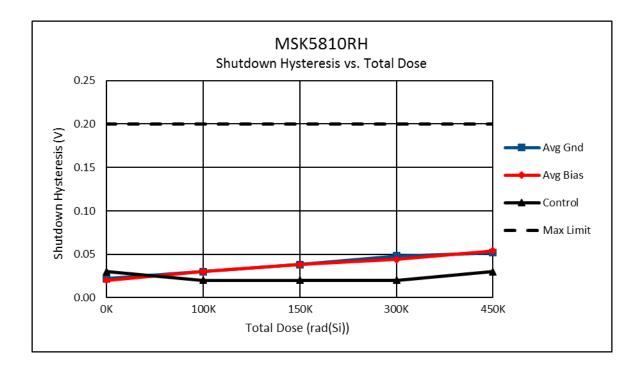


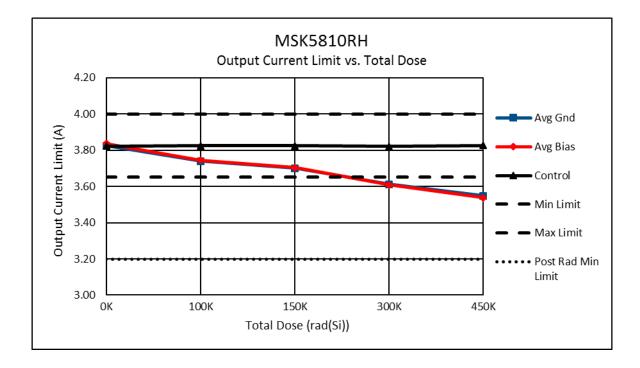












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH - 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3rd Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH - 5th Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test) December 10, 2010 (MSK 5810RH - 7th Test) April 1, 2011 (MSK5810RH – 8th Test) July 8, 2011 (MSK5810RH – 9<sup>th</sup> Test) June 14, 2013 (MSK5810RH - 10th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#13) June 14, 2013 (MSK5810RH – 11th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#21) November 6, 2013 (MSK5810RH - 12th Test, IC Wafer Lot: W10809524.1 #8 Transistor Wafer Lot: CJ302831RC#20) August 28, 2015 (MSK5810RH - 13th Test, IC Wafer Lot: WP005144.1 Transistor Wafer Lot: P741F1002 #21) November 8, 2016 (MSK5810RH – 14th Test, IC Wafer Lot: WP005144.1 #9 Transistor Wafer Lot: PF01F1005 #6) March 29, 2017 (MSK5810RH - 15th Test, IC Wafer Lot: WP005144.1 #8 Transistor Wafer Lot: PF01F1005 #6) September 15, 2017 (MSK5810RH – 16th Test, IC Wafer Lot: W10809524.1 #8 Transistor Wafer Lot: DL153631 #3) January 12, 2018 (MSK5810RH – 17<sup>th</sup> Test, IC Wafer Lot: WP005144.1 #8 Transistor Wafer Lot: P741F1002 #21)

> B. Horton N. Kresse J. Joy

Anaren, Inc. - MSK Products

The total dose radiation test plan for the MSK5810RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK5810RH.

### II. Radiation Source:

Total dose was performed at the University of Massachusetts, Lowell, using a Cobalt 60 radiation source. The dose rate was determined to be 126.7 Rads(Si)/sec. The total dose schedule can be found in Table I.

# III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 160 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, two control devices were tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation, the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as two control devices, at each total dose level. The time to complete electrical tests exceeded 1 hour at the 100krad(Si) and 150krad(Si) dose levels due to test equipment malfunctions. Electrical tests were completed within one hour of irradiation at 300krad(Si) and 450krad(Si). Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field at all test points.

# IV. <u>Data</u>:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting Anaren Inc. – MSK Products.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing and statistical analysis, Feedback Voltage, Shutdown Threshold, Shutdown Hysteresis and Output Current Limit exhibited shift due to irradiation, however all performance curves stayed within specification beyond 300 Krad(Si) TID. MSK5810RH Biased/Unbiased Dose Rate Schedule

Dosimetry Equipmer	nt
Bruker Biospin # 016	2

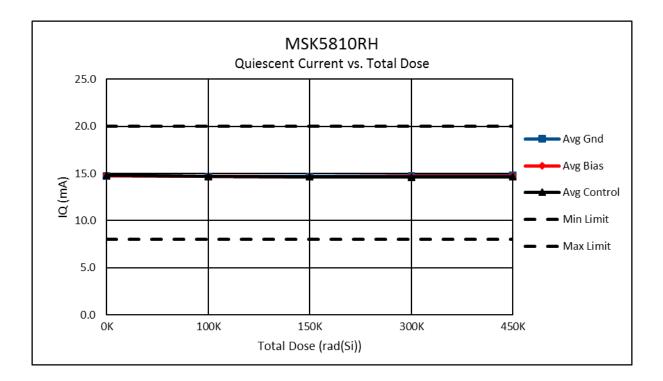
Irradiation Date	
1-12-17	

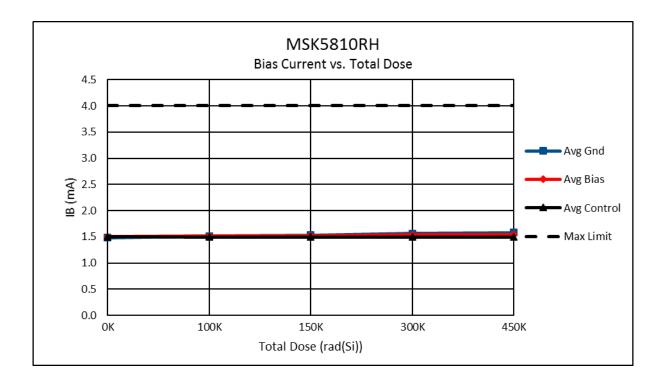
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
13:33	103,00	103,000
6:46	51,500	154,500
20:19	154,500	309,000
20:19	154,500	463,500

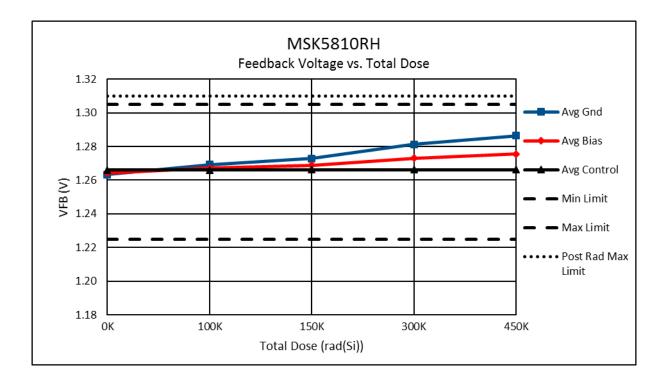
	0000	0004	0000	0000 0004	
Biased S/N -	- 0020,	0021,	0022,	0023, 0024	

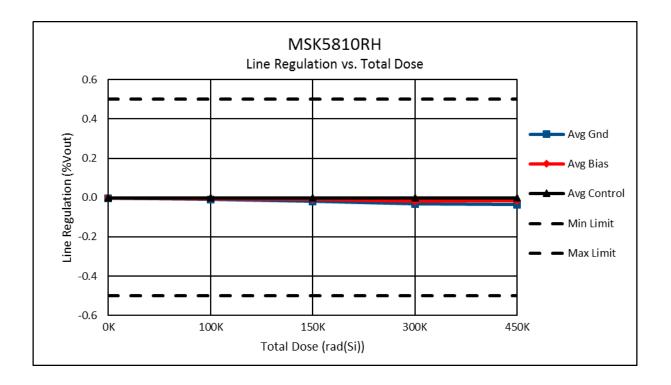
Unbiased S/N – 0015, 0016, 0017, 0018, 0019

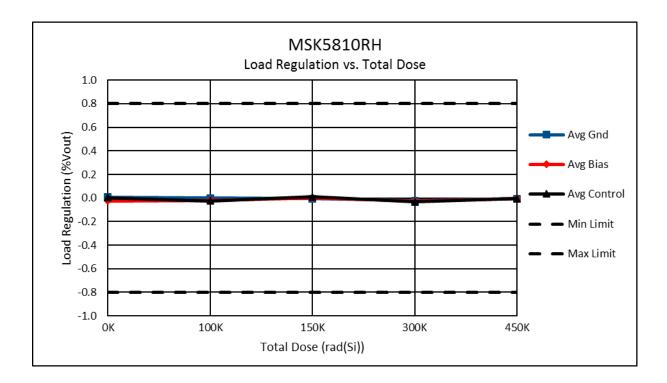
Table 1

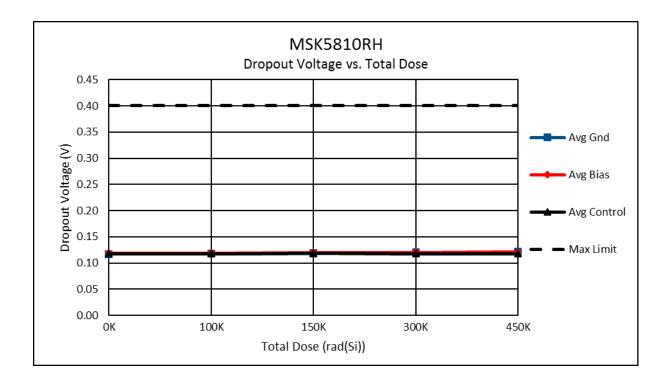


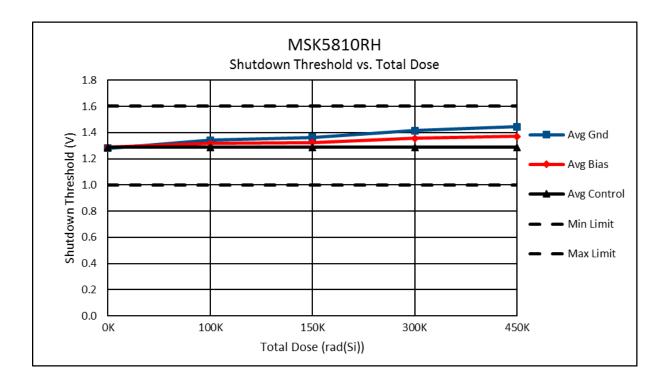


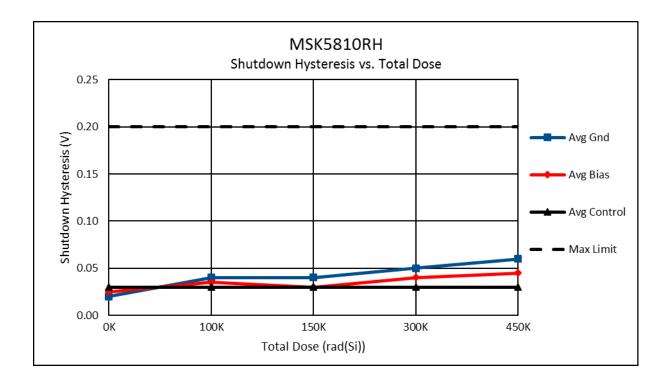


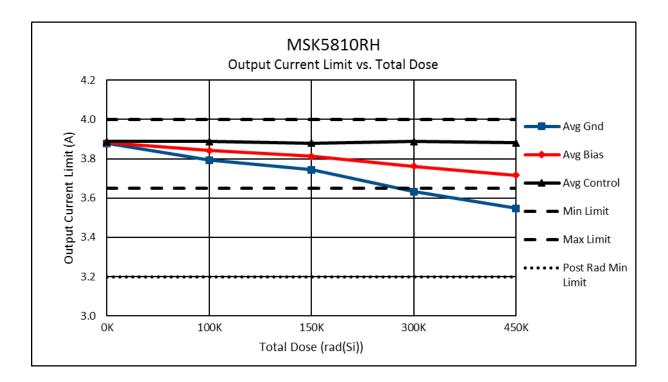












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH - 5th Test) September 17, 2010 (MSK 5810RH - 6th Test) December 10, 2010 (MSK 5810RH - 7th Test) April 1, 2011 (MSK5810RH – 8<sup>th</sup> Test) July 8, 2011 (MSK5810RH – 9th Test) June 14, 2013 (MSK5810RH – 10th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#13) June 14, 2013 (MSK5810RH – 11th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#21) November 6, 2013 (MSK5810RH – 12th Test, IC Wafer Lot: W10809524.1 #8 Transistor Wafer Lot: CJ302831RC#20) August 28, 2015 (MSK5810RH - 13th Test, IC Wafer Lot: WP005144.1 Transistor Wafer Lot: P741F1002 #21) November 8, 2016 (MSK5810RH – 14th Test, IC Wafer Lot: WP005144.1 #9 Transistor Wafer Lot: PF01F1005 #6) March 29, 2017 (MSK5810RH - 15th Test, IC Wafer Lot: WP005144.1 #8 Transistor Wafer Lot: PF01F1005 #6) September 15, 2017 (MSK5810RH - 16th Test, IC Wafer Lot: W10809524.1 #8 Transistor Wafer Lot: DL153631 #3)

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Anaren, Inc. - MSK Products

The total dose radiation test plan for the MSK5810RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK5810RH.

#### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a Cobalt 60 radiation source. The dose rate was determined to be 141 Rads(Si)/sec. The total dose schedule can be found in Table I.

#### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 160 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, two control devices were tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation, the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as two control devices, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting Anaren Inc. – MSK Products.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing and statistical analysis, Feedback Voltage, Shutdown Threshold, Shutdown Hysteresis and Output Current Limit exhibited shift due to irradiation, however all performance curves stayed within specification beyond 300 Krad(Si) TID.

MSK5810RH Biased/Unbiased Dose Rate Schedule

Dosimetry Equipment	
Bruker Biospin # 0162	

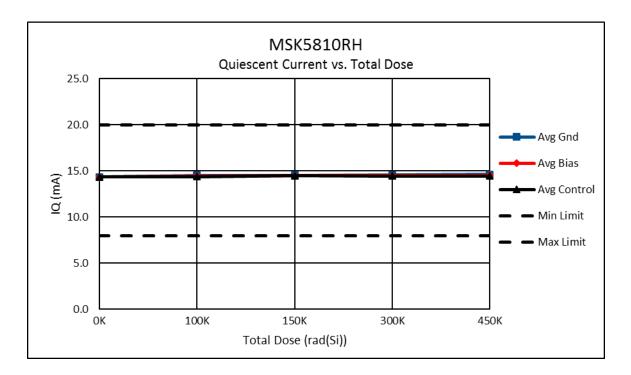
Irradiation Date
9/15/17

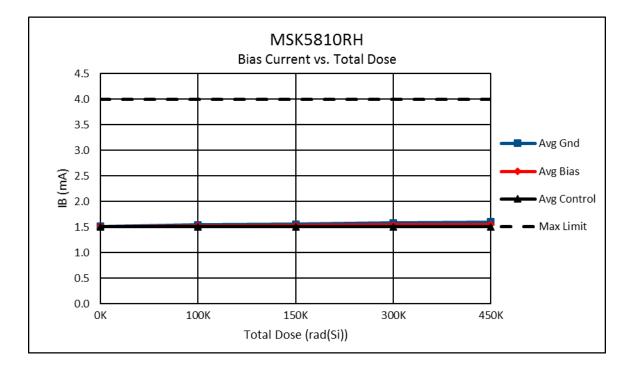
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
12:10	103,000	103,000
6:05	51,500	154,500
18:16	154,500	309,000
18:16	154,500	463,500

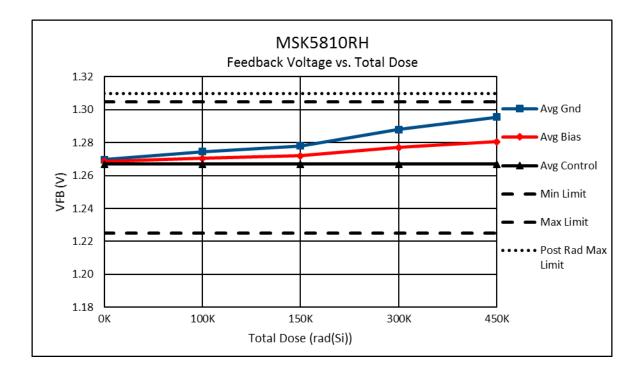
Biased S/	– 1458, 1459, 1460, 1461, 1462

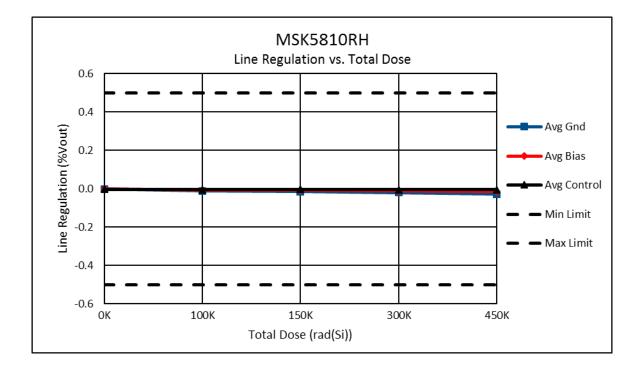
Unbiased S/N – 14	63. 1464.	1465, 1466	. 1467
	00, 1+0+,	1400, 1400	, 1407

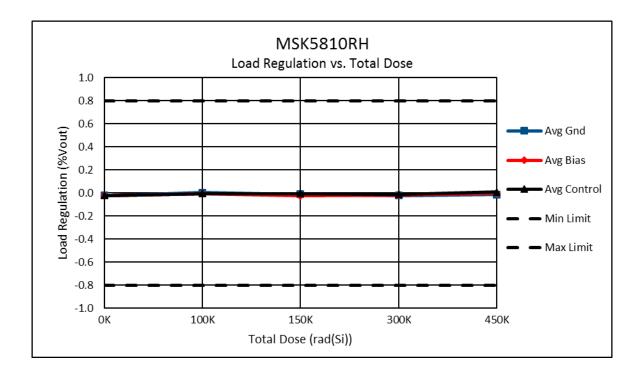
Table 1

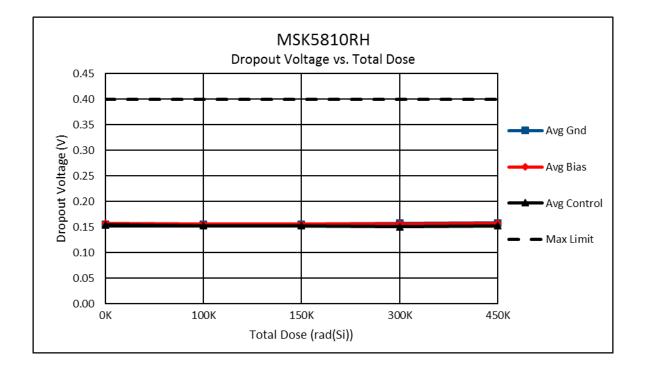


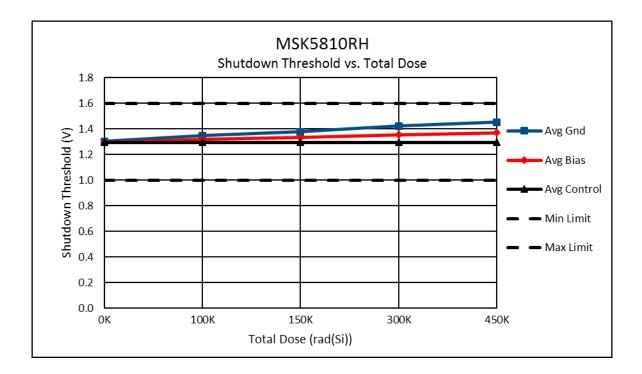


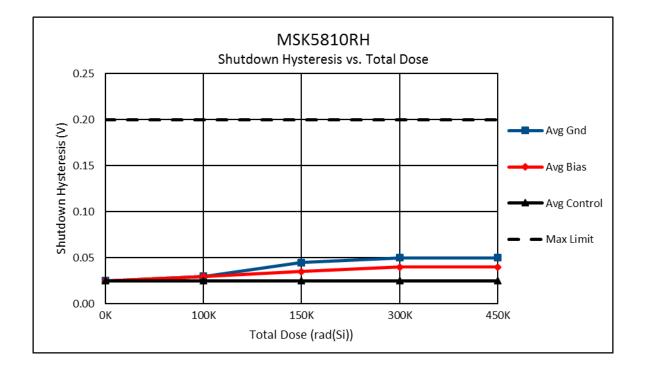


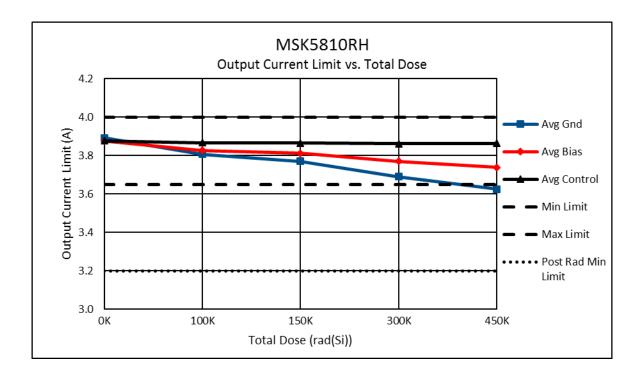












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1st Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH - 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH - 3rd Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH - 5th Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test) December 10, 2010 (MSK 5810RH - 7<sup>th</sup> Test) April 1, 2011 (MSK5810RH – 8th Test) July 8, 2011 (MSK5810RH – 9th Test) June 14, 2013 (MSK5810RH - 10th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#13) June 14, 2013 (MSK5810RH – 11th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#21) November 6, 2013 (MSK5810RH – 12<sup>th</sup> Test, IC Wafer Lot: W10809524.1 #8 Transistor Wafer Lot: CJ302831RC#20) August 28, 2015 (MSK5810RH - 13th Test, IC Wafer Lot: WP005144.1 Transistor Wafer Lot: P741F1002 #21) November 8, 2016 (MSK5810RH – 14th Test, IC Wafer Lot: WP005144.1 #9 Transistor Wafer Lot: PF01F1005 #6) March 29, 2017 (MSK5810RH - 15th Test, IC Wafer Lot: WP005144.1 #8 Transistor Wafer Lot: PF01F1005 #6)

> B. Horton P. Dinneen N. Kresse

MSK Products – Anaren Inc.

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

#### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 151 Rads(Si)/sec. The total dose schedule can be found in Table I.

#### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, two control devices were tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation, the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting Anaren Inc. – MSK Products.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing and statistical analysis, Feedback Voltage, Shutdown Threshold, and Shutdown Hysteresis exhibited shift due to irradiation, however all performance curves stayed within specification beyond 300 Krad(Si) TID.

A Line Regulation data point was an outlier at 300 Krad(Si) but was within family at 100 Krad(Si) and 450 Krad(Si). We can conclude that this was a testing error and therefore removed the data point from the analysis.

MSK 5810RH Biased/Unbiased Dose Rate Schedule

Dosimetry Equipment Bruker Biospin # 0162

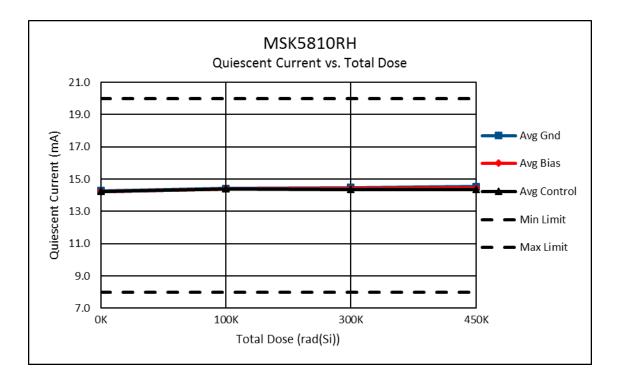
rradiation Date
3/29/17

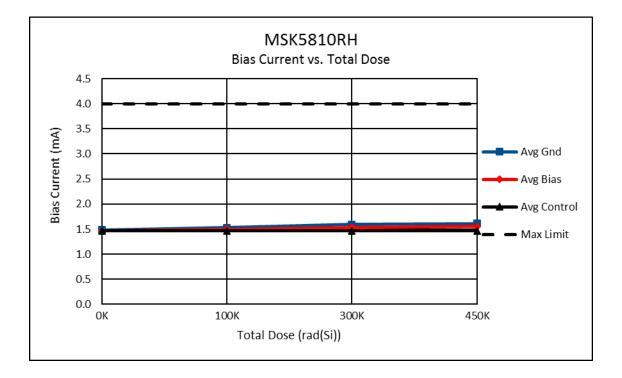
Exposure Length (min:sec)	rade(Si)	Cumulative Dose rads(Si)
11:23	103,000	100,300
22:46	206,000	309,000
17:05	154,500	463,500

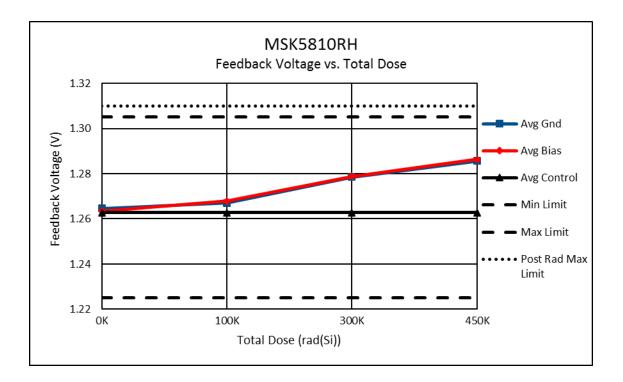
Biased S/N – 1366, 1367, 1368, 1369, 1370

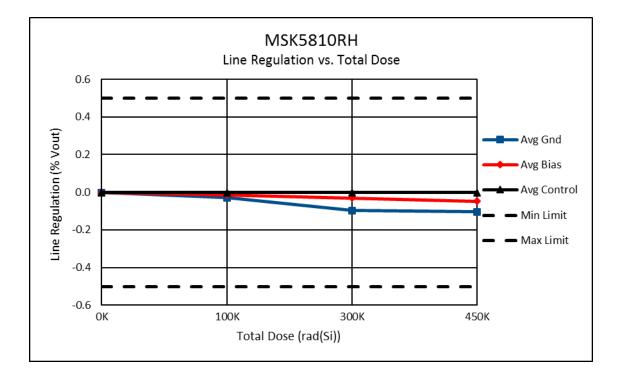
Unbiased S/N – 1371, 1372, 1373, 1374, 1375

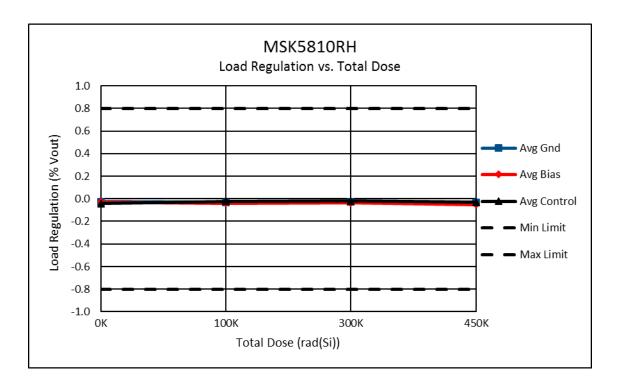
Table 1

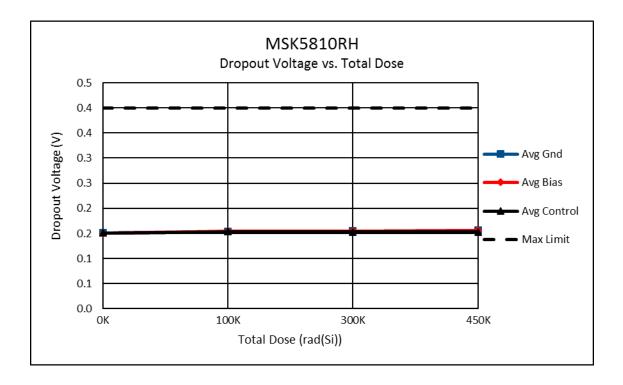


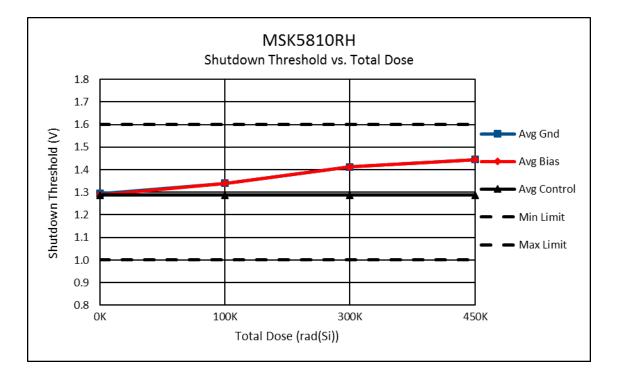


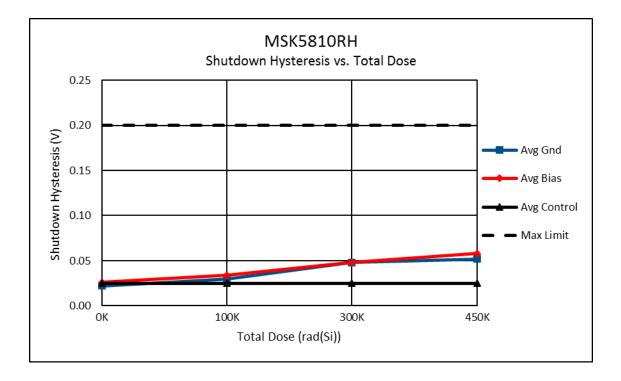


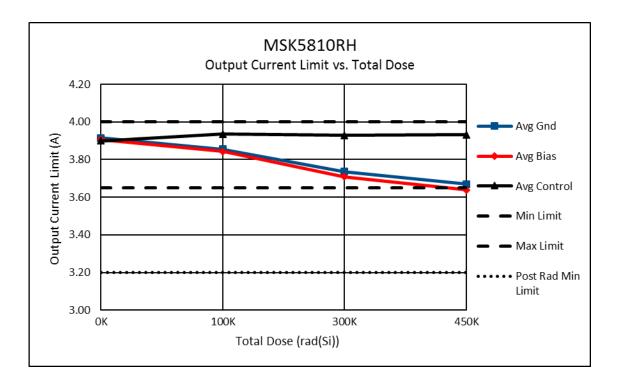












MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH - 1st Test) March 26, 2009 (MSK 5810RH - 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH - 5<sup>th</sup> Test) September 17, 2010 (MSK 5810RH - 6th Test) December 10,2010 (MSK 5810RH - 7<sup>th</sup> Test) April 1, 2011 (MSK5810RH – 8<sup>th</sup> Test) July 8, 2011 (MSK5810RH – 9th Test) June 14, 2013 (MSK5810RH – 10th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#13) June 14, 2013 (MSK5810RH – 11th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#21) November 6, 2013 (MSK5810RH – 12th Test, IC Wafer Lot: W10809524.1 #8 Transistor Wafer Lot: CJ302831RC#20) August 28, 2015 (MSK5810RH - 13th Test, IC Wafer Lot: WP005144.1 Transistor Wafer Lot: P741F1002 #21) November 8, 2016 (MSK5810RH – 14<sup>th</sup> Test, IC Wafer Lot: WP005144.1 #9 Transistor Wafer Lot: PF01F1005 #6) B. Horton F. Freytag

J. Joy

N. Kresse

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

# II. Radiation Source:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 158 Rads(Si)/sec. The total dose schedule can be found in Table I.

# III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting Anaren Inc. – MSK Products.

# V. <u>Summary</u>:

Based on the test data recorded during radiation testing and statistical analysis, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID

MSK 5810RH Biased/Unbiased Dose Rate Schedule

Dosimetry Equipment	
Bruker Biospin # 0162	

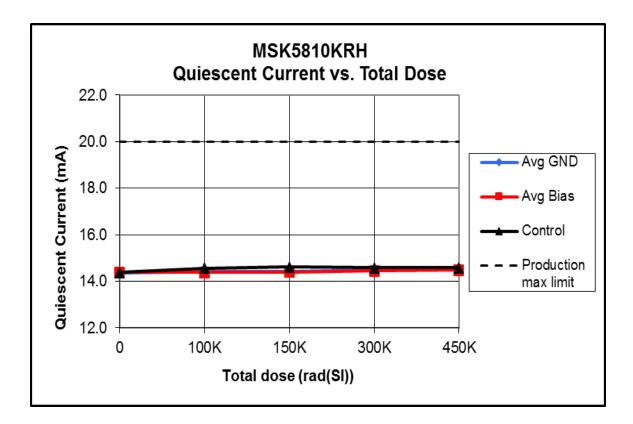
Irradiation Date	
11/8/16	

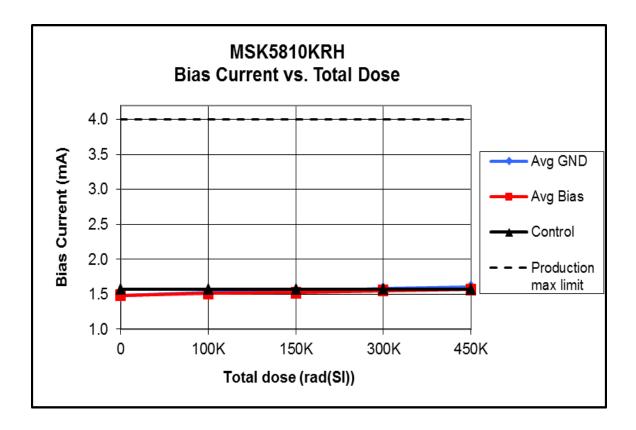
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
0:10:35	100,300	100,300
0:05:17	50,100	150,400
0:15:52	150,400	300,800
0:15:52	150,400	451,200

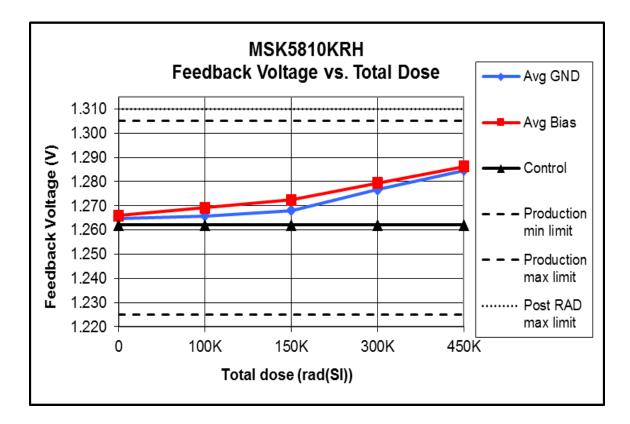
Biased S/N - 1344, 1345, 1346, 1347, 1348

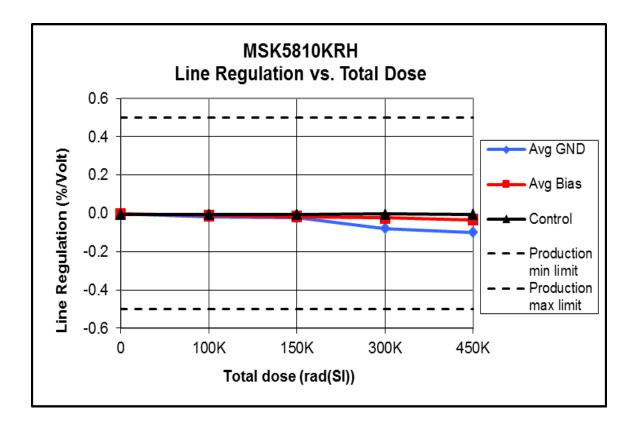
Unbiased S/N – 1	349, 1350,	1351.	1352.	1353
	0+0, 10000	, 1001,	1002,	1000

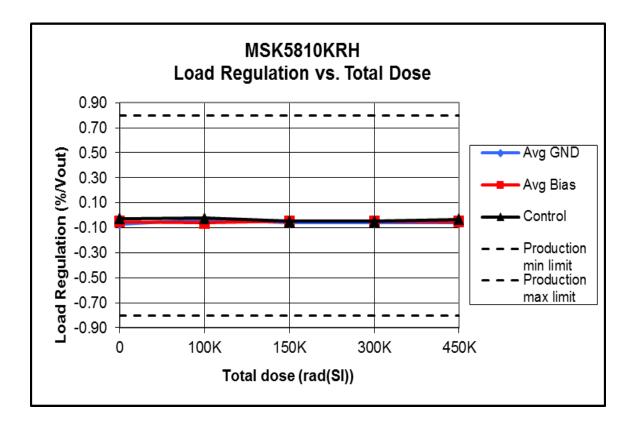
# Table 1

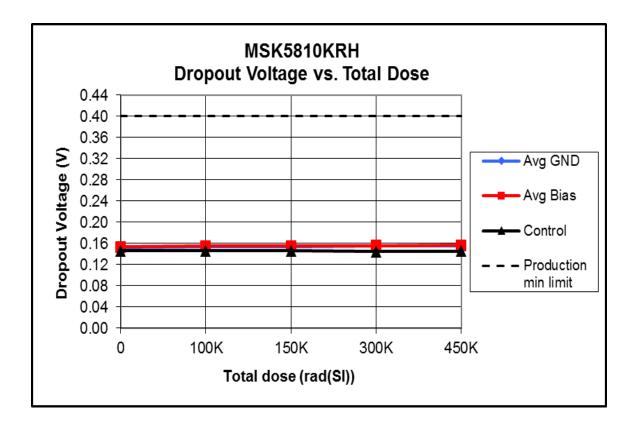


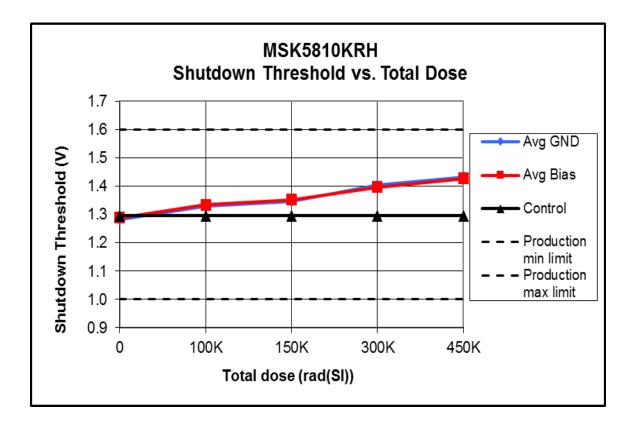


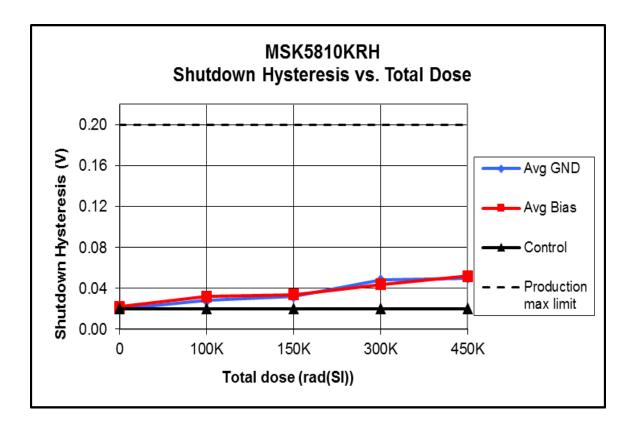


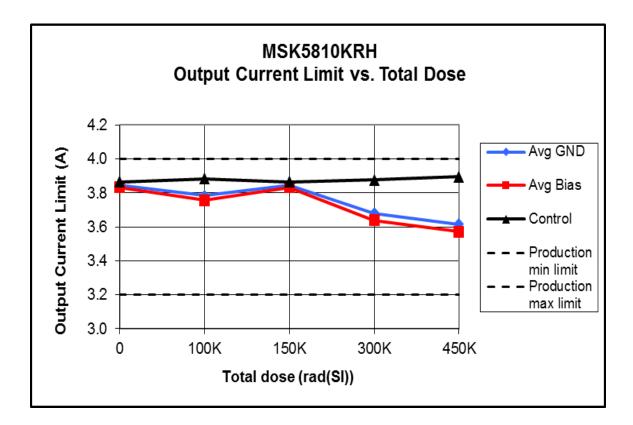












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK5810RH - 2<sup>nd</sup> Test) September 3, 2009 (MSK5810RH – 3rd Test) November 6, 2009 (MSK5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK5810RH - 5th Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test) December 10,2010 (MSK 5810RH - 7th Test) April 1, 2011 (MSK5810RH – 8th Test) July 8, 2011 (MSK5810RH - 9th Test) June 14, 2013 (MSK5810RH - 10th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#13) June 14, 2013 (MSK5810RH - 11th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot:CJ302831#21) November 6, 2013 (MSK5810RH – 12<sup>th</sup> Test, IC Wafer Lot: W10809524.1 #8 Transistor Wafer Lot:CJ302831RC#20) August 28, 2015 (MSK5810RH - 13th Test, IC Wafer Lot: WP005144.1 Transistor Wafer Lot: P741F1002 #21)

B. Horton

C. Salce

MSK Products, Anaren Inc.

The total dose radiation test plan for the MSK5810RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

#### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 109 Rads(Si)/sec. The total dose schedule can be found in Table I.

#### III. <u>Test Setup</u>:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting MSK.

### V. <u>Summary</u>:

Dosimetry Equipment	
Bruker Biospin # 0162	

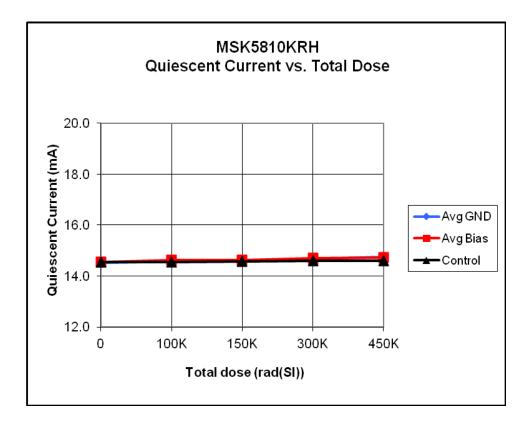
Irradiation Date	
8/28/15	

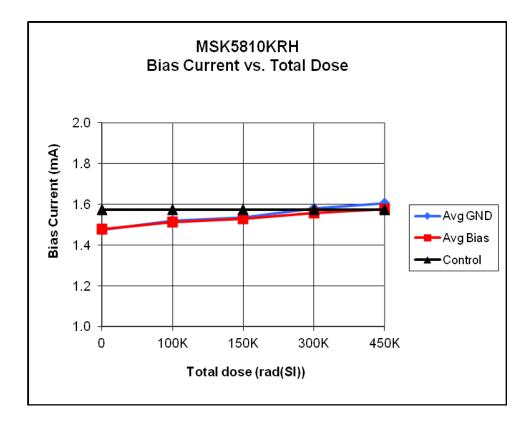
Exposure Length (min:sec)		Cumulative Dose rads(Si)
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07:53	51,557	154,562
23:38	154,562	309,124
23:38	154,562	463,686

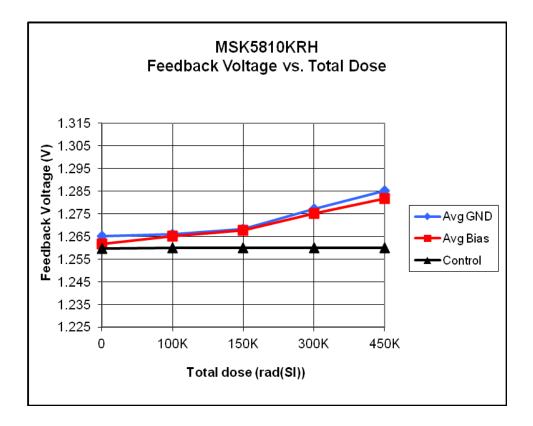
Biased S/N - 1228,	1229,	1230,	1232,	1233

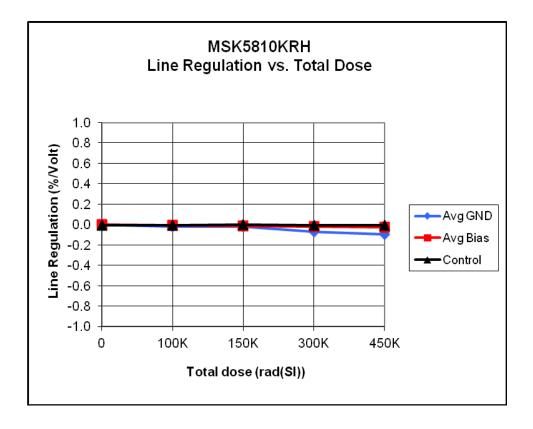
35, 1236, 1237, 1238	Unbiased S/N – 1234, 1235
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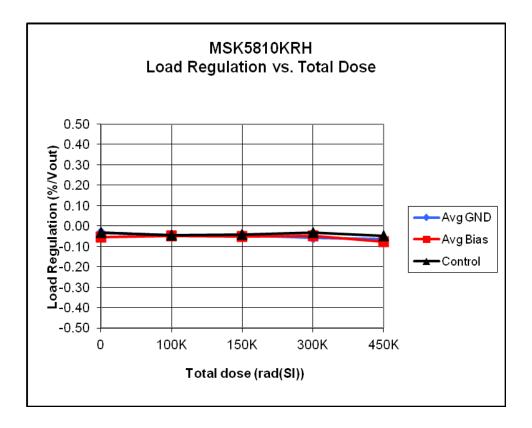
Table 1

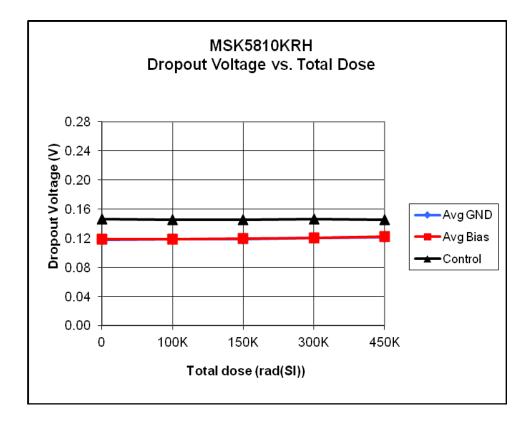


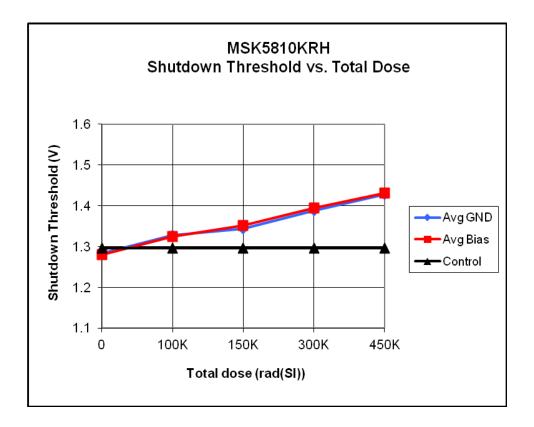


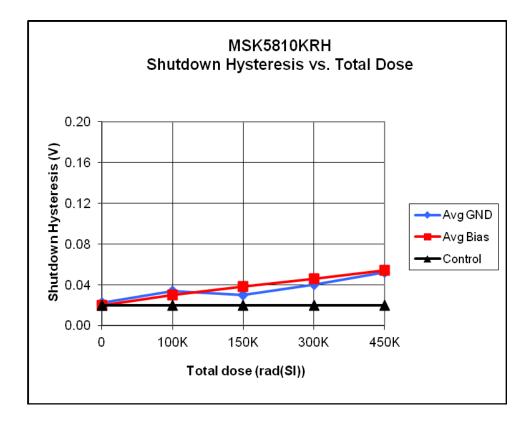


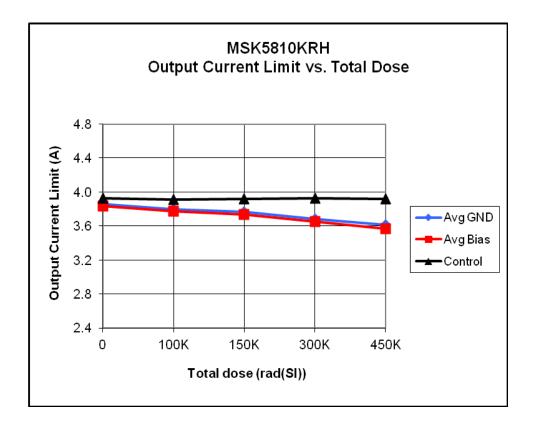












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1st Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH - 1st Test) March 26, 2009 (MSK 5810RH - 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH - 3rd Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH - 5th Test) September 17, 2010 (MSK 5810RH - 6th Test) December 10,2010 (MSK 5810RH - 7<sup>th</sup> Test) April 1, 2011 (MSK5810RH – 8th Test) July 8, 2011 (MSK5810RH – 9<sup>th</sup> Test) June 14, 2013 (MSK5810RH – 10th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#13) June 14, 2013 (MSK5810RH - 11th Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot:CJ302831#21) November 6, 2013 (MSK5810RH – 12th Test, IC Wafer Lot: W10809524.1 #8 Transistor Wafer Lot:CJ302831RC#20)

> B. Horton R. Wakeman

M.S. Kennedy Corporation Liverpool, NY

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 88 Rads(Si)/sec. The total dose schedule can be found in Table I.

#### III. <u>Test Setup</u>:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

#### V. <u>Summary</u>:

Dosimetry Equipment	
Bruker Biospin # 0162	

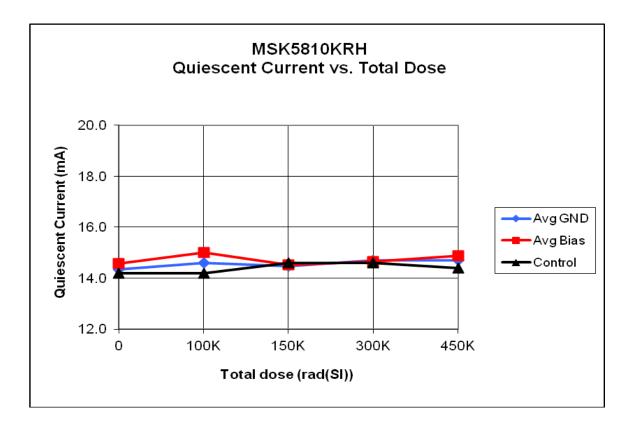
Irradiation Date	
11/6/13	

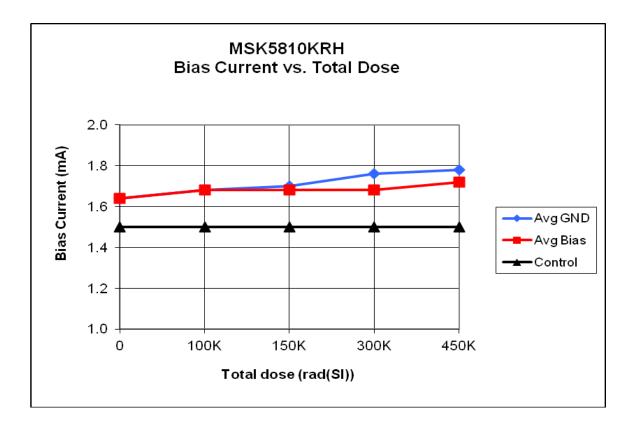
Exposure Length (min:sec)		Cumulative Dose rads(Si)
0:19:31	103,048	103,048
0:09:46	51,568	154,616
0:29:16	154,528	309,144
0:29:16	154,528	463,672

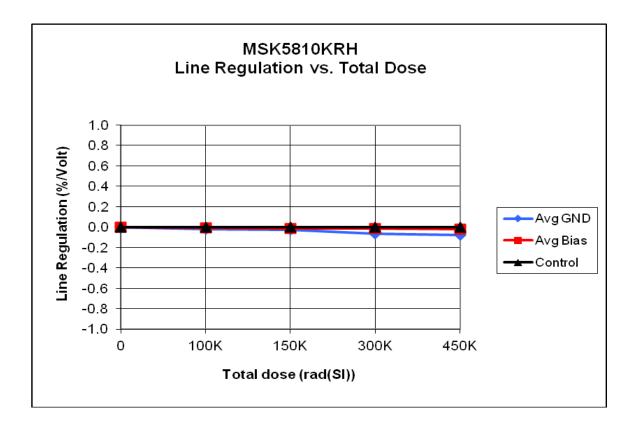
Biased S/N -	- 1072, 1073	3, 1075, 1076, <sup>-</sup>	1077
Blaced C/H		0, 1010, 1010,	

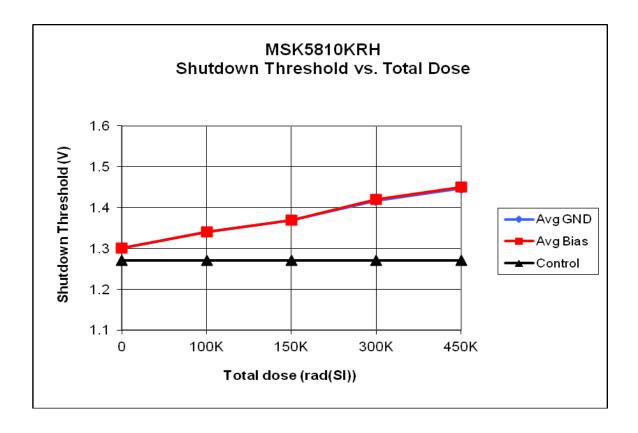
Unbiased S/N - 1078, 1079, 1080, 1081, 1082

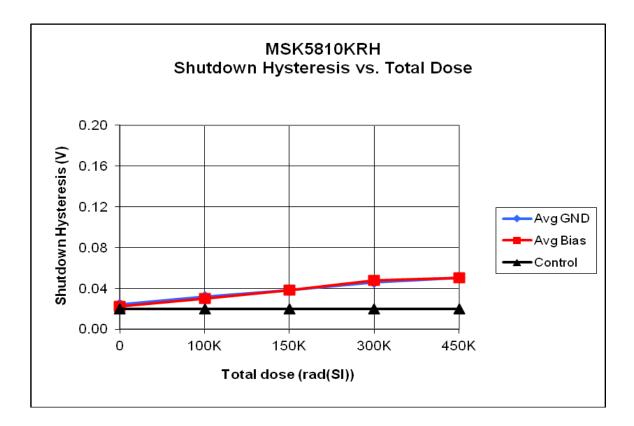
Table 1

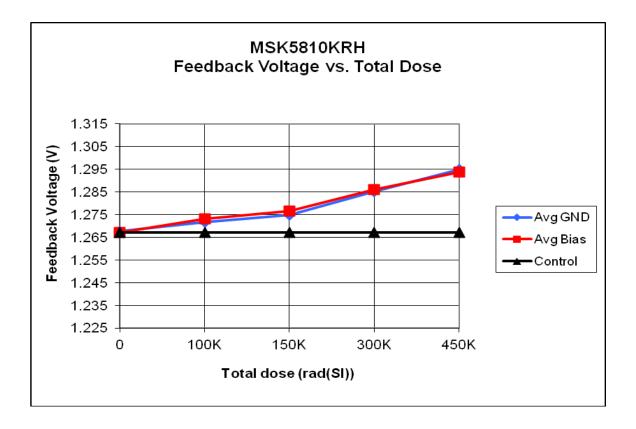


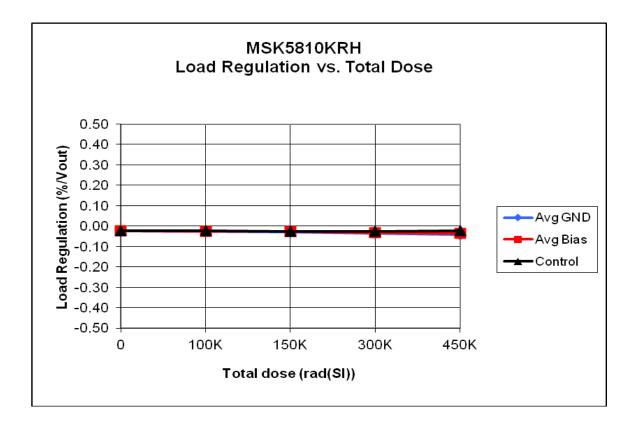


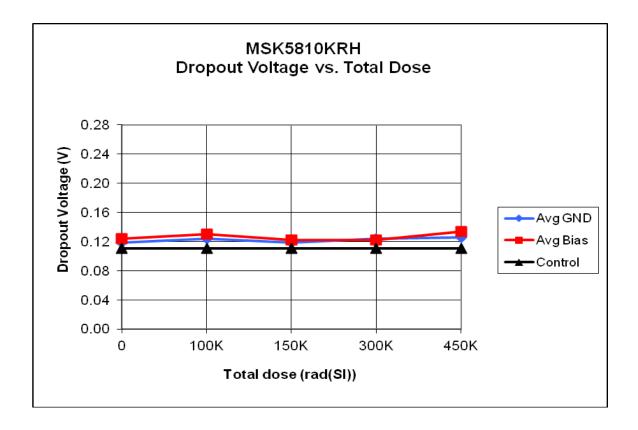


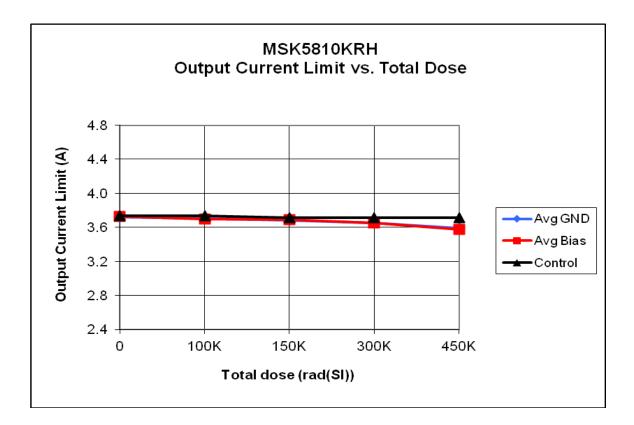












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH – 5<sup>th</sup> Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test) December 10,2010 (MSK 5810RH – 7<sup>th</sup> Test) April 1, 2011 (MSK5810RH – 8<sup>th</sup> Test) July 8, 2011 (MSK5810RH – 9<sup>th</sup> Test) July 8, 2011 (MSK5810RH – 9<sup>th</sup> Test) June 14, 2013 (MSK5810RH – 10<sup>th</sup> Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#13) June 14, 2013 (MSK5810RH – 10<sup>th</sup> Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#21)

> B. Horton C. Salce P. Dinneen

M.S. Kennedy Corporation Liverpool, NY

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 93 Rads(Si)/sec. The total dose schedule can be found in Table I.

### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

### V. <u>Summary</u>:

Dosimetry Equipment	
Bruker Biospin # 0162	

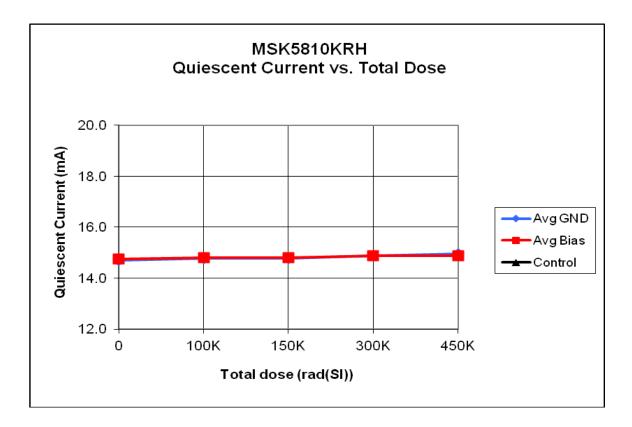
Irradiation Date	
6/14/13	

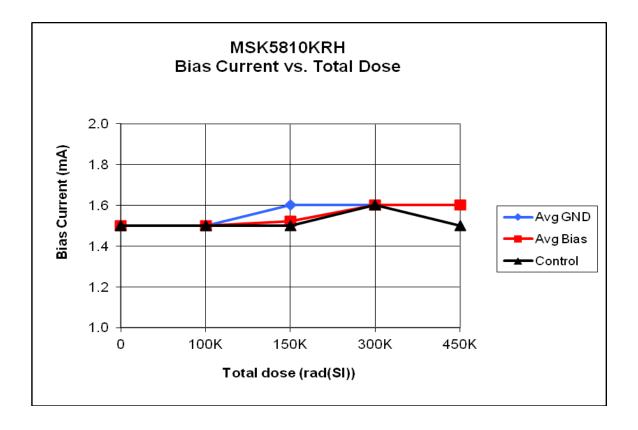
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
18:28	103,044	103,044
9:14	51,522	154,566
27:42	154,566	309,132
27:42	154,566	463,698

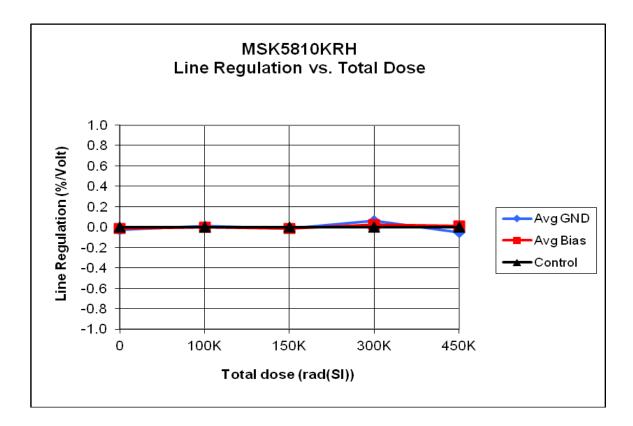
Biased S/N - 0991, 0992, 0993, 0994, 0995

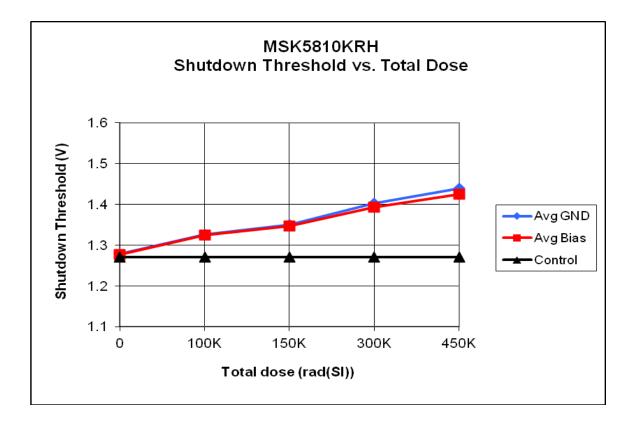
nbiased S/N – 0996, 0997, 0998, 0999, 1000
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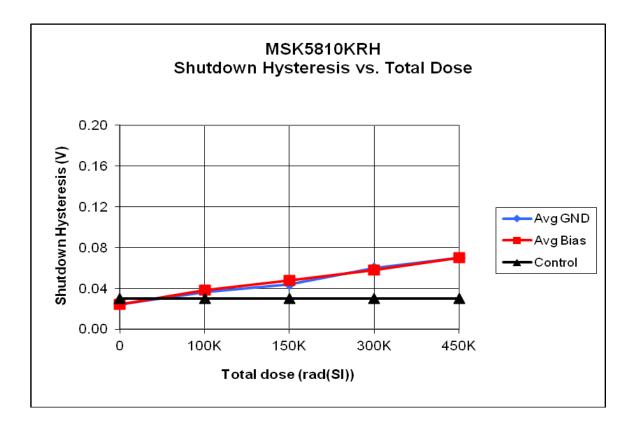
Table 1

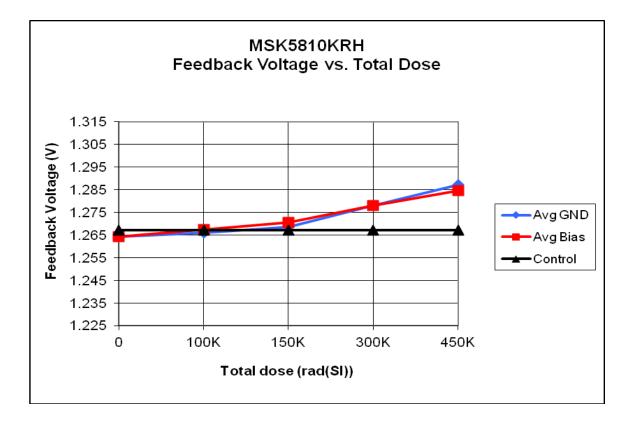


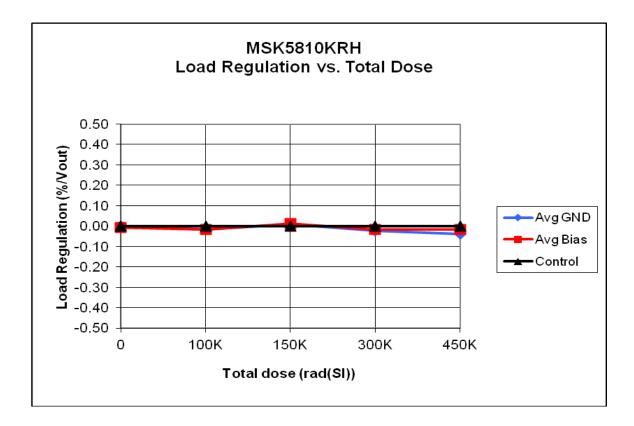


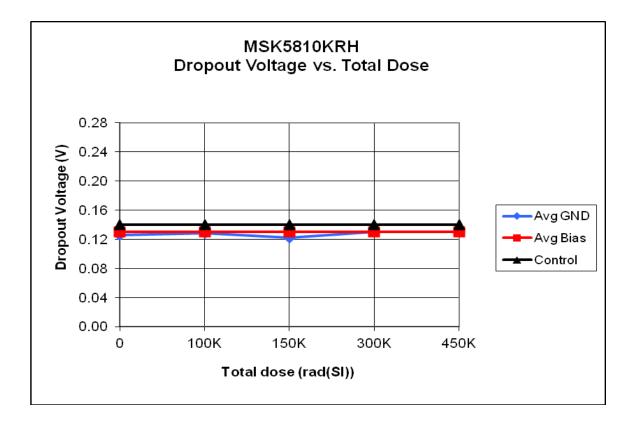


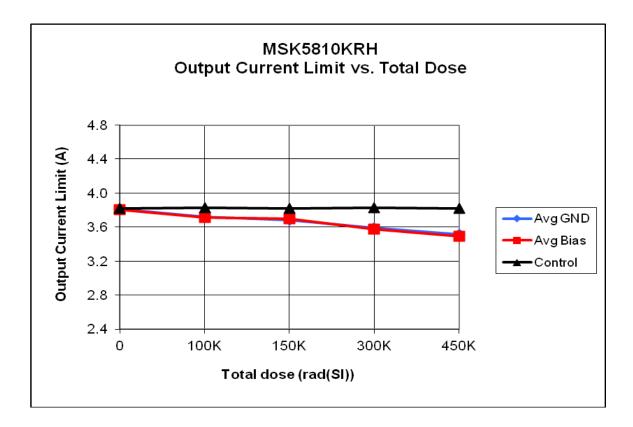












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH – 5<sup>th</sup> Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test) December 10,2010 (MSK 5810RH – 7<sup>th</sup> Test) April 1, 2011 (MSK5810RH – 8<sup>th</sup> Test) July 8, 2011 (MSK5810RH – 9<sup>th</sup> Test) July 8, 2011 (MSK5810RH – 9<sup>th</sup> Test) June 14, 2013 (MSK5810RH – 10<sup>th</sup> Test, IC Wafer Lot: WD0051441#9 Transistor Wafer Lot: CJ302831#13)

> B. Horton C. Salce P. Dinneen

M.S. Kennedy Corporation Liverpool, NY

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

### II. Radiation Source:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 93 Rads(Si)/sec. The total dose schedule can be found in Table I.

### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

## V. <u>Summary</u>:

Dosimetry Equipment	
Bruker Biospin # 0162	

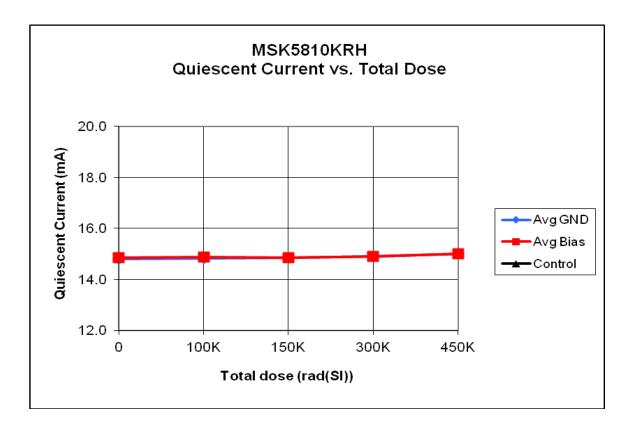
Irradiation Date	
6/14/13	

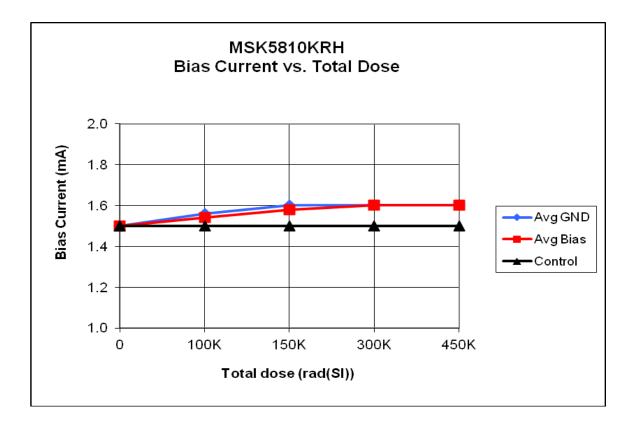
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27:42	154,566	309,132
27:42	154,566	463,698

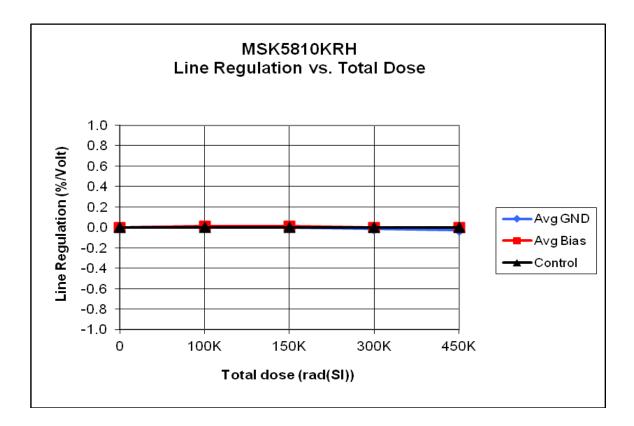
Biased S/N – 0979, 0980, 0981, 0982, 0983

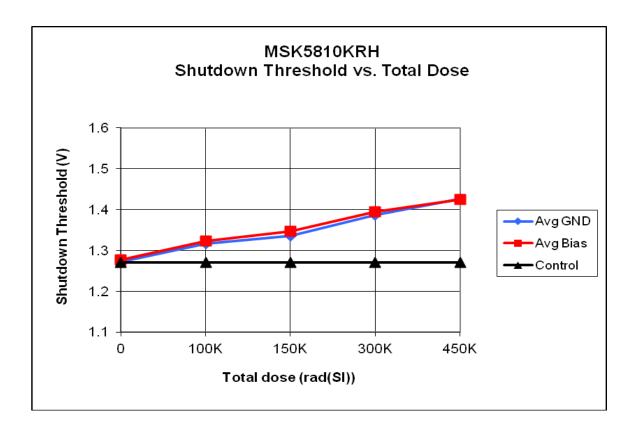
Unbiased S/N - 0984, 0985, 0986, 0987, 0988

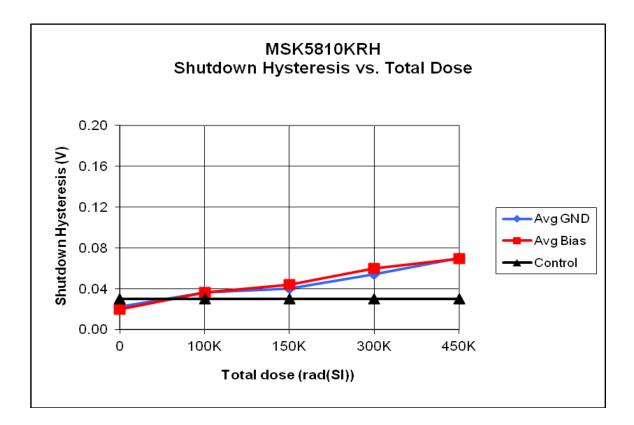
Table 1

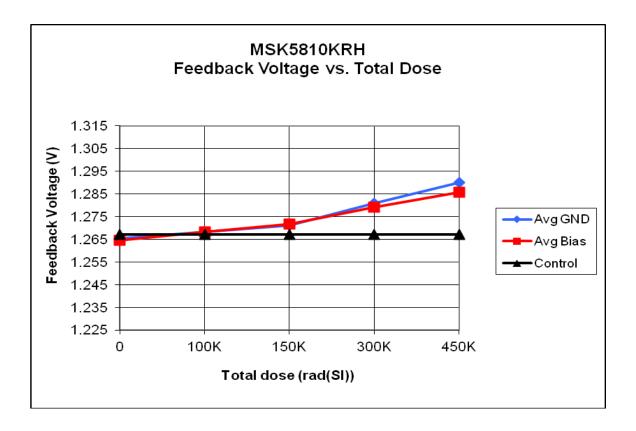


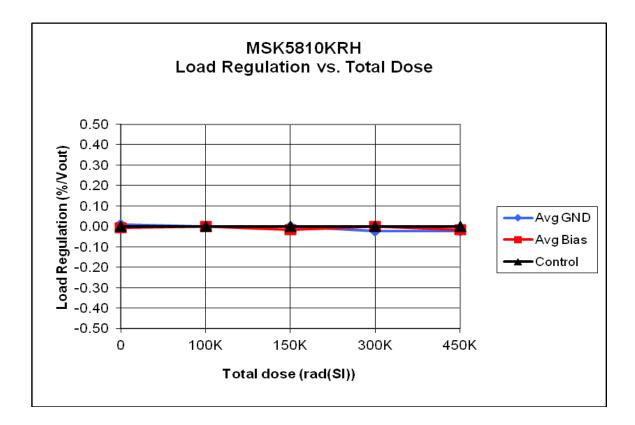


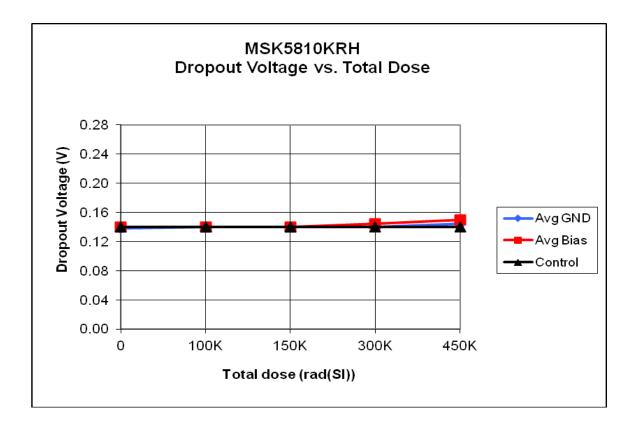


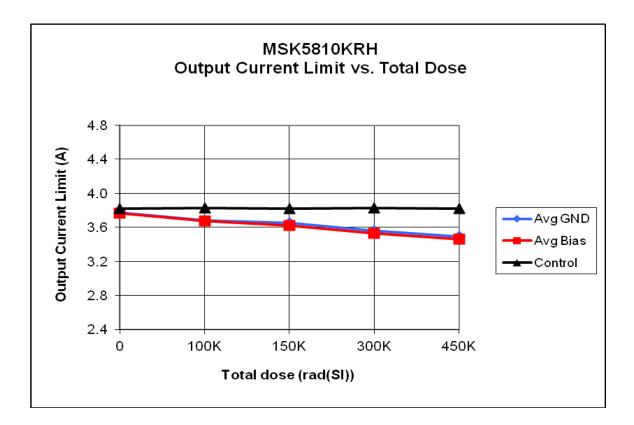












## MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH – 5<sup>th</sup> Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test) December 10,2010 (MSK 5810RH – 7<sup>th</sup> Test) April 1, 2011 (MSK5810RH – 8<sup>th</sup> Test) July 8, 2011 (MSK5810RH – 9<sup>th</sup> Test)

> B. Horton C. Salce

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 122 Rads(Si)/sec. The total dose schedule can be found in Table I.

### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID

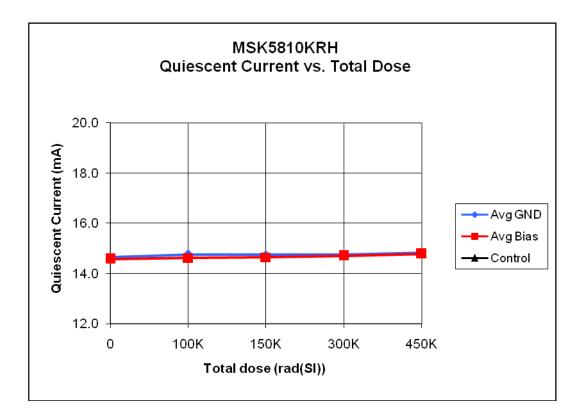
Dosimetry Equipment	
Bruker Biospin # 0162	2

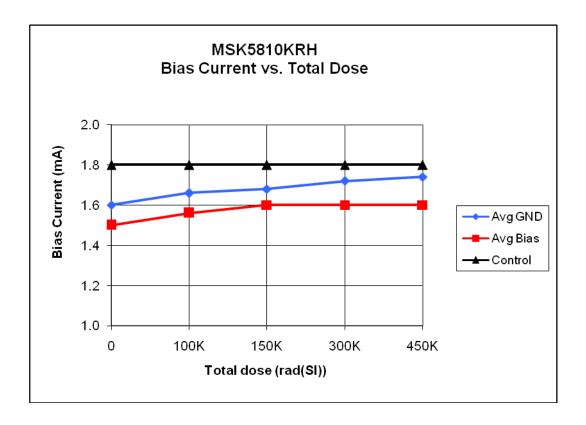
7/8/11	Irradiation Date	
1/0/11	7/8/11	

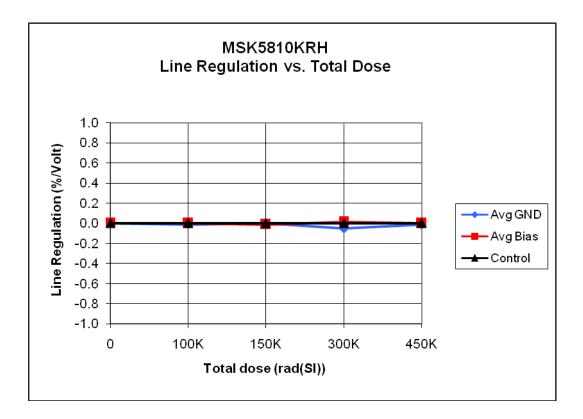
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
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7:02	51,484	154,574
21:06	154,452	309,026
21:06	154,452	463,478

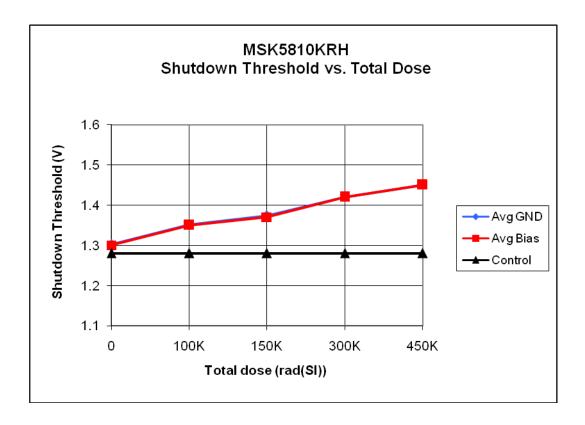
Biased S/N – 0673, 0674, 0675, 0676, 0677

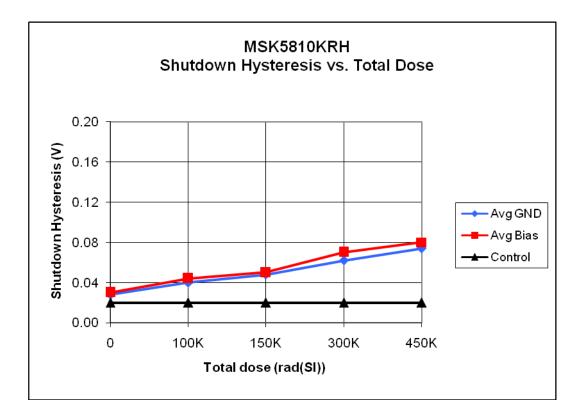
Table 1

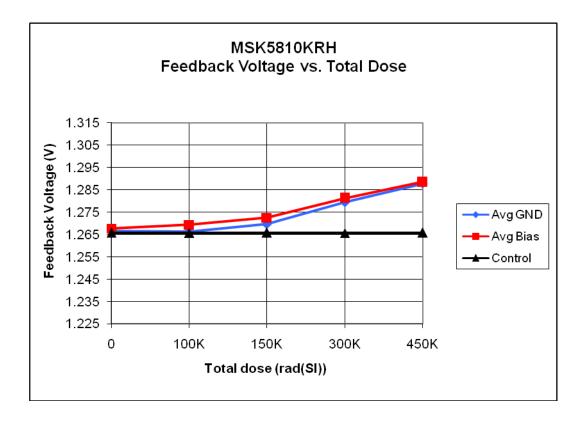


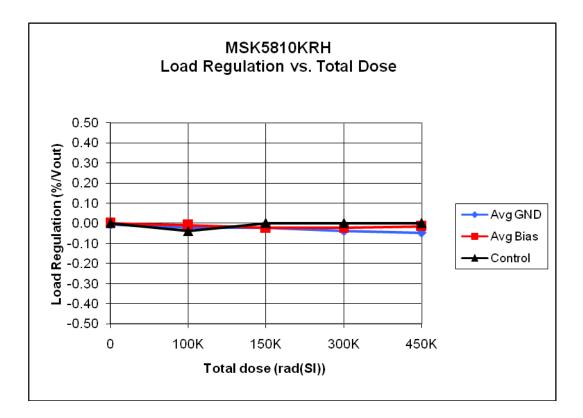


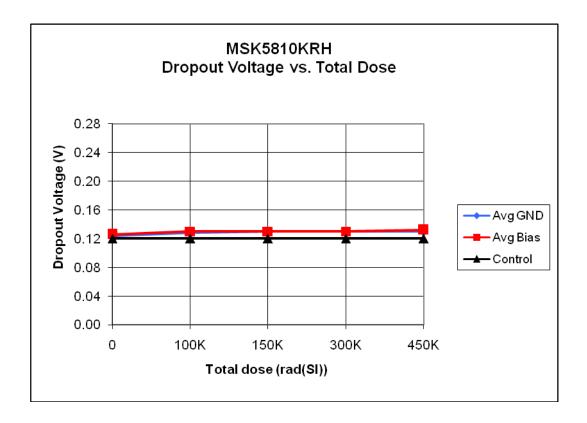


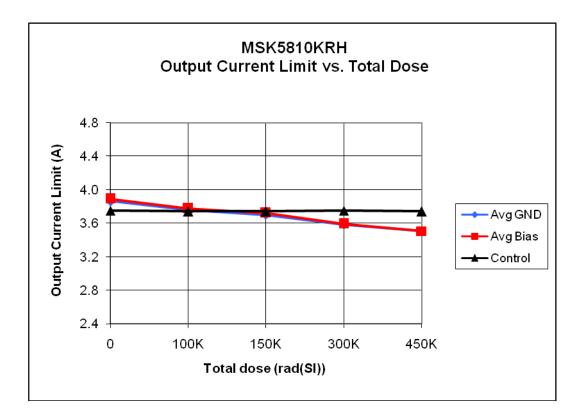












## MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH – 5<sup>th</sup> Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test) December 10,2010 (MSK 5810RH – 7<sup>th</sup> Test) April 1, 2011 (MSK5810RH – 8<sup>th</sup> Test)

> M. Bilecki B. Erwin

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

#### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 125 Rads(Si)/sec. The total dose schedule can be found in Table I.

#### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID

Dosimetry Equipment	
Bruker Biospin # 0162	

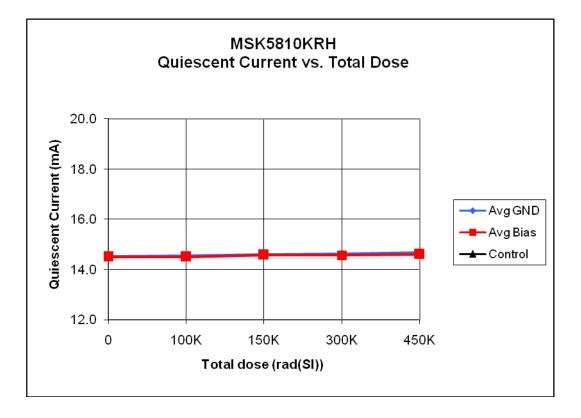
Irradiation Date
4/1/11

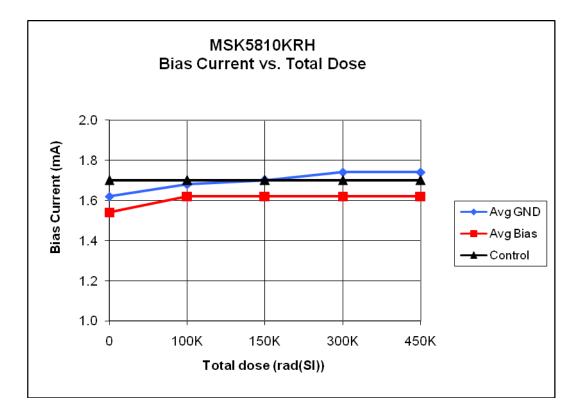
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
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6:52	51,500	154,500
20:36	154,500	309,000
20:36	154,500	463,500

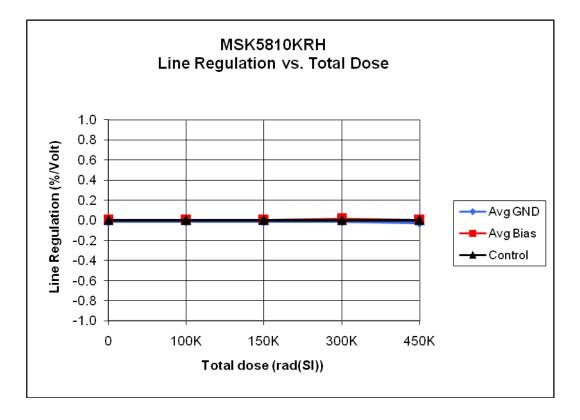
Biased S/N - 0762, 0763, 0764, 0765, 0766

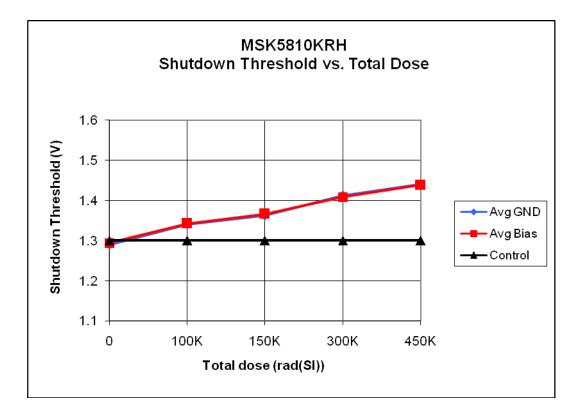
Unbiased S/N – 0757, 0758, 0759, 0760, 0761
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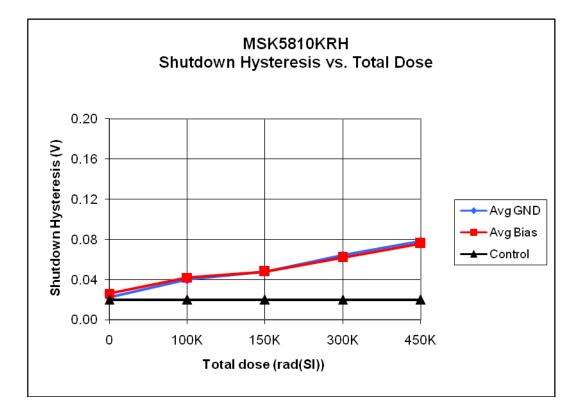
## Table 1

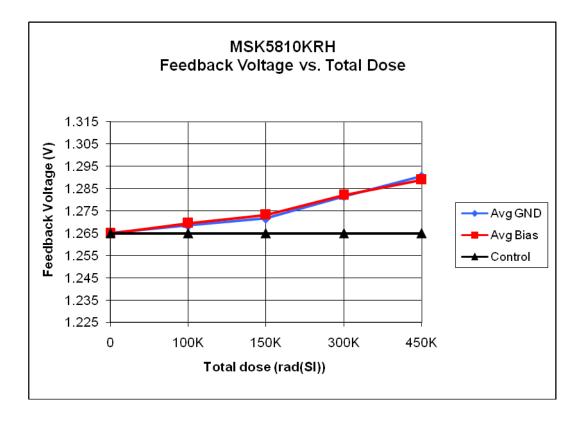


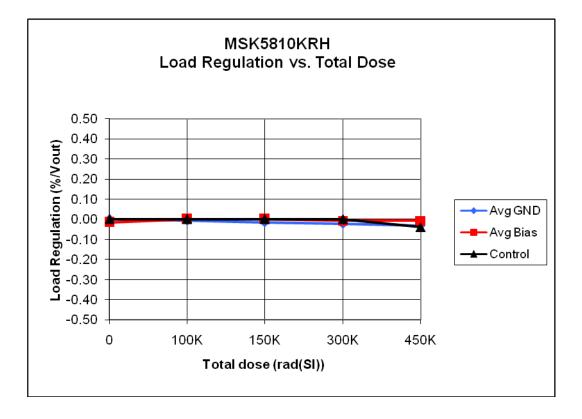


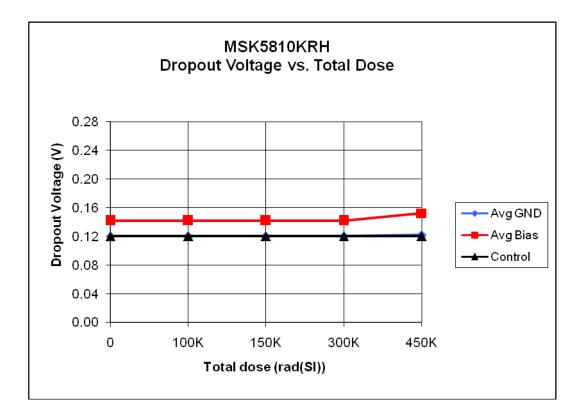


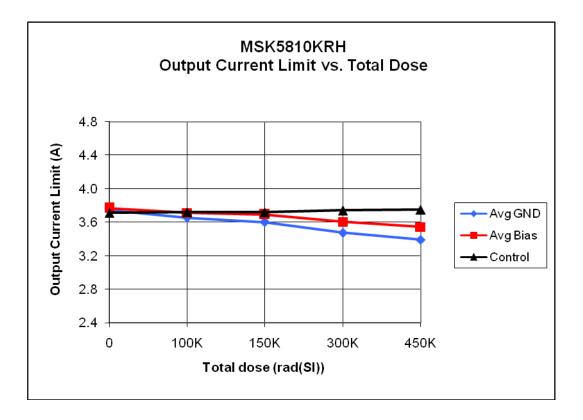












## MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH – 5<sup>th</sup> Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test) December 10,2010 (MSK 5810RH – 7<sup>th</sup> Test)

> B. Erwin R. Wakeman

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

#### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 132 Rads(Si)/sec. The total dose schedule can be found in Table I.

#### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Nine devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Four devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID

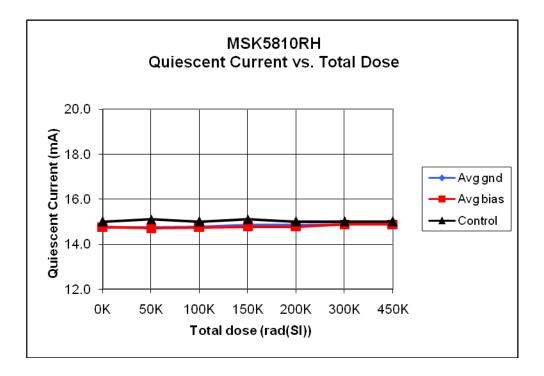
Dosimetry Equipment	
Bruker Biospin # 0162	

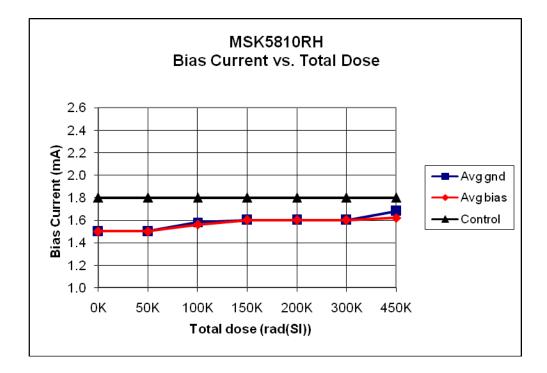
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12/10/10

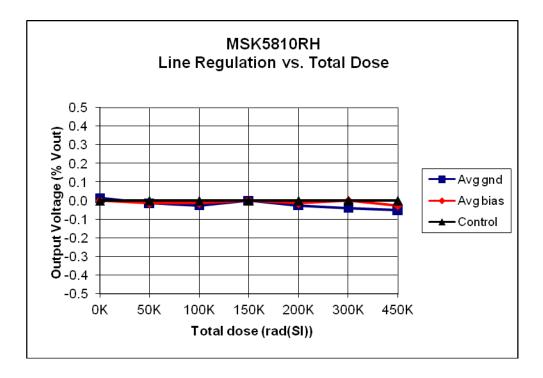
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
6:43	51,584	51,584
6:43	51,584	103,168
6:43	51,584	154,752
6:43	51,584	206,336
13:25	103,040	309,376
20:07	154,496	463,872

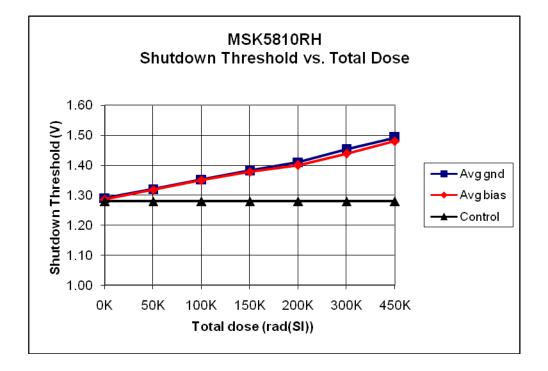
Biased S/N – 0538, 0539, 0540, 0541, 0542
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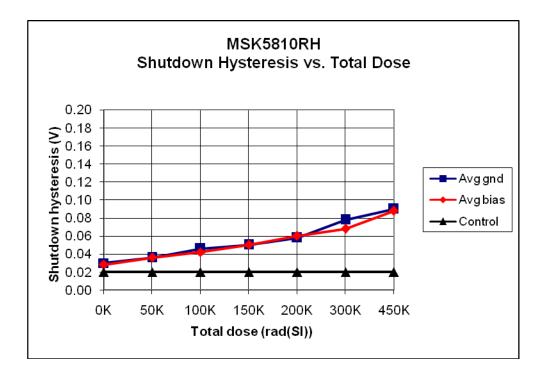
Table 1

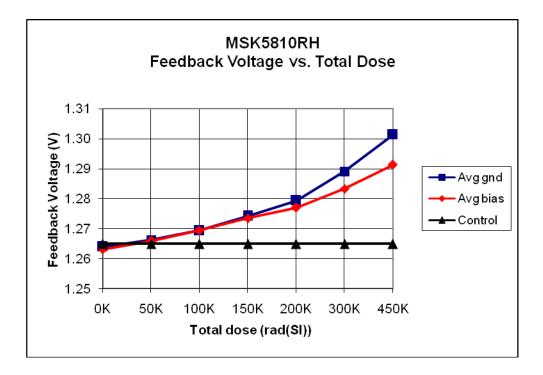


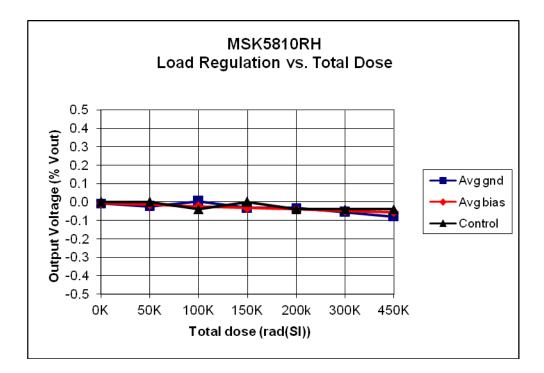


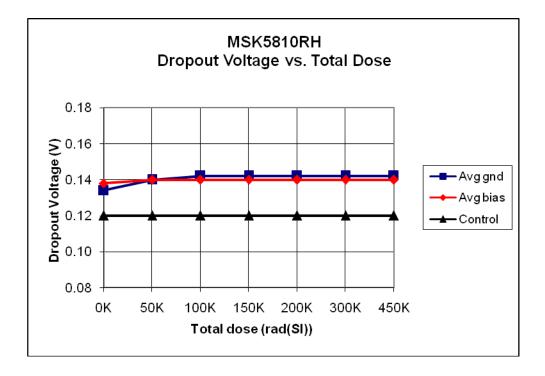


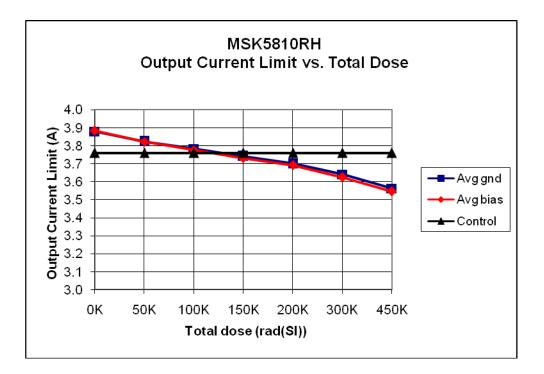












## MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH – 5<sup>th</sup> Test) September 17, 2010 (MSK 5810RH – 6<sup>th</sup> Test)

> B. Horton R. Wakeman

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 132 Rads(Si)/sec. The total dose schedule can be found in Table I.

#### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Nine devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Four devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 300 KRAD (Si) TID.

Dosimetry Equipment	
Bruker Biospin # 0162	

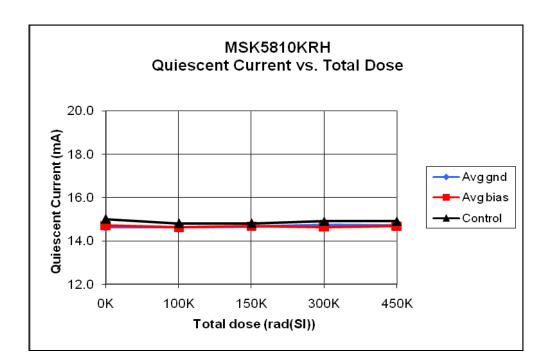
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09/17/10	

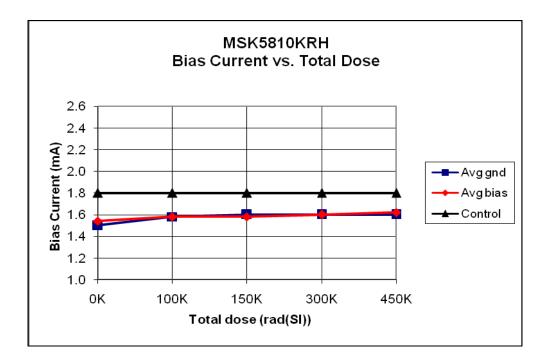
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
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6:30	51,480	154,440
19:31	154,572	309,012
19:31	154,572	463,584

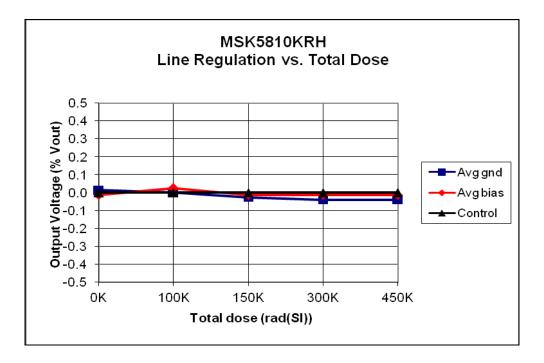
Biased S/N – 0476, 0477, 0478, 0	480

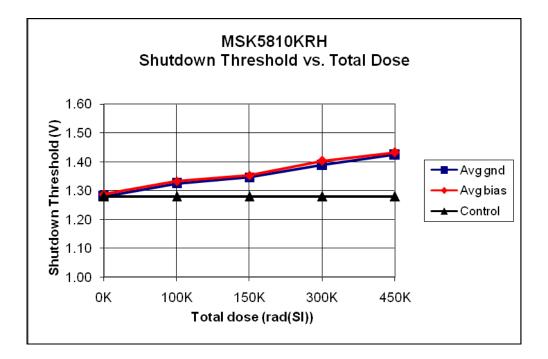
Unbiased S/N – 0471, 0472, 0473, 0474, 0475	Unbiased S/N	- 0471, 04	472, 0473	, 0474,	0475
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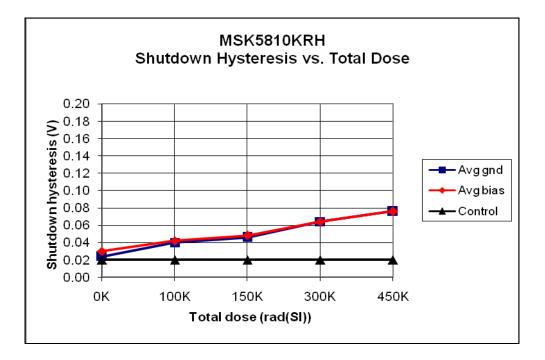
Table 1

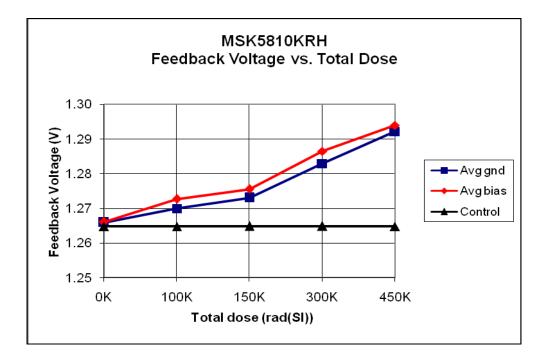


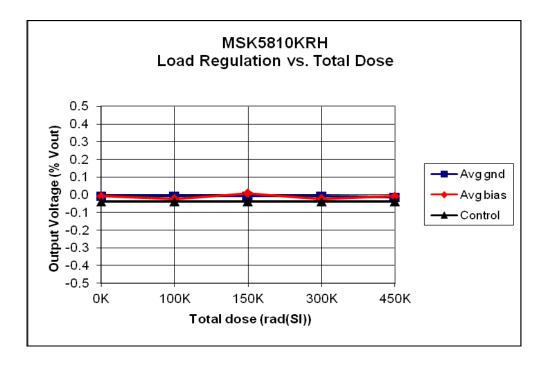


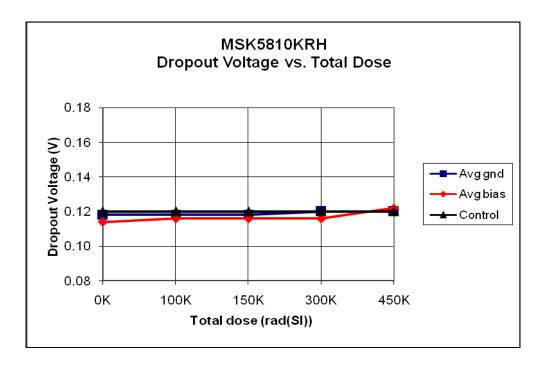


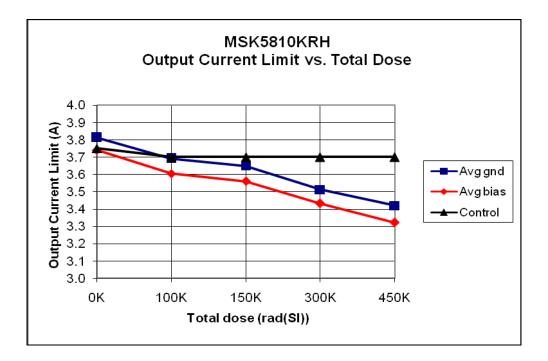












## MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test) May 14, 2010 (MSK 5810RH – 5<sup>th</sup> Test)

> M. Bilecki B. Erwin

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

### II. Radiation Source:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 138 Rads(Si)/sec. The total dose schedule can be found in Table I.

#### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

### V. <u>Summary</u>:

Based on the test data recorded during radiation testing, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID.

Dosimetry Equipment	
Bruker Biospin # 0141	

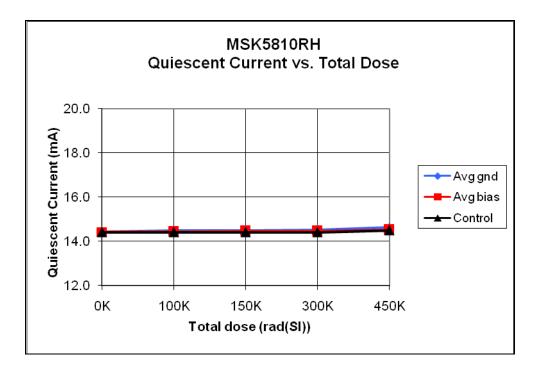
I	rradiation Date	
	05/14/10	

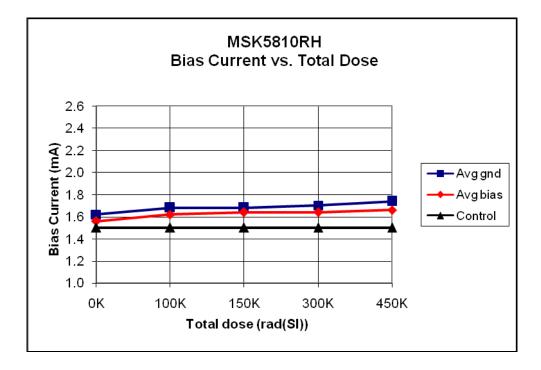
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
12:27	103,086	103,086
6:14	51,612	154,698
18:40	154,560	309,258
18:40	154,560	463,818

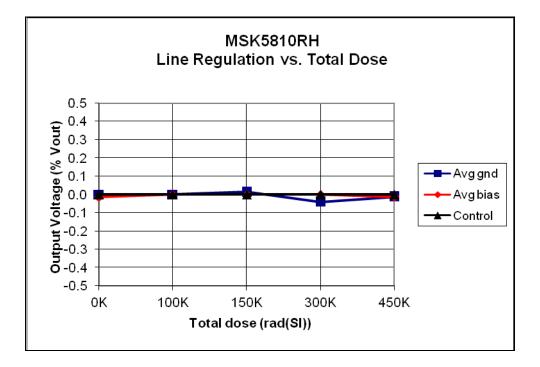
Biased S/N - 0360, 0361, 0362, 0363, 0364

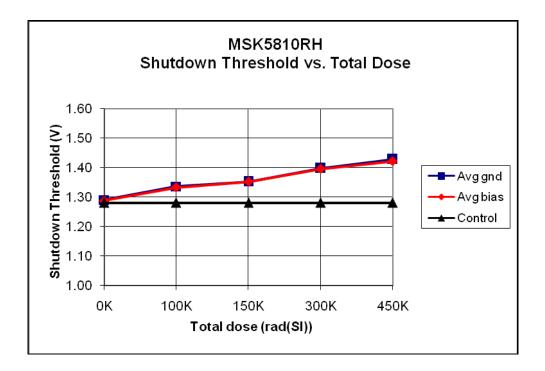
Unbiased S/N – 0365, 0366, 0367, 0368, 0369	Unbiased S/N –	0365,	0366,	0367,	0368,	0369
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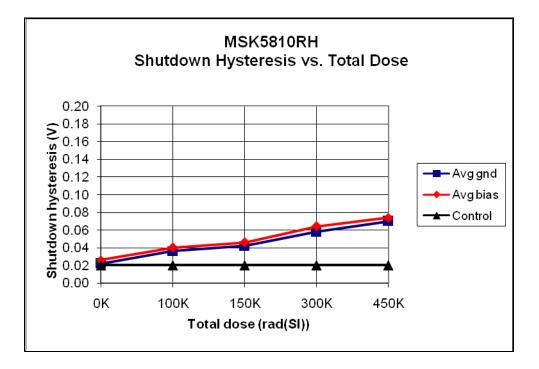
Table 1

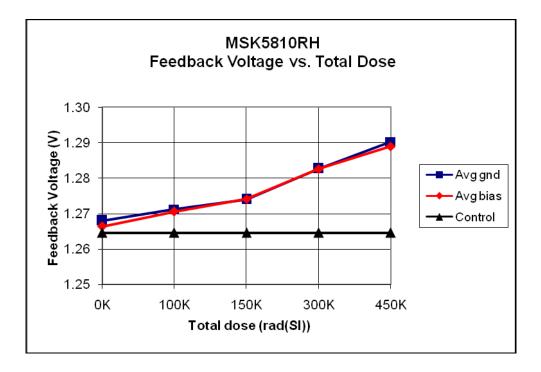


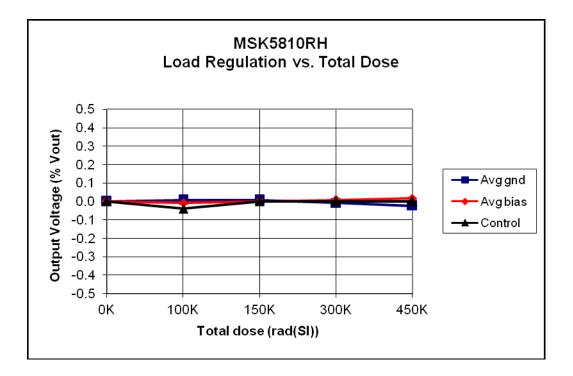


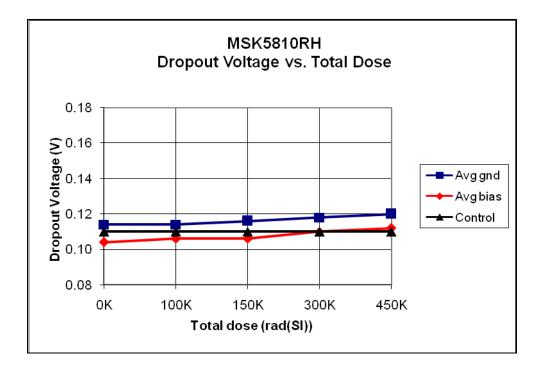


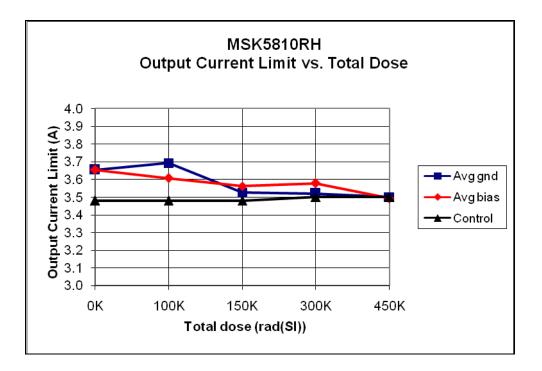












## MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH, MSK 5827RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (MSK 5810RH – 1<sup>st</sup> Test) Updated on December 24, 2008 March 21, 2009 (MSK 5822RH – 1<sup>st</sup> Test) March 26, 2009 (MSK 5810RH – 2<sup>nd</sup> Test) September 3, 2009 (MSK 5810RH – 3<sup>rd</sup> Test) November 6, 2009 (MSK 5810RH – 4<sup>th</sup> Test)

> M. Bilecki B. Erwin

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK 5800RH, MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

## II. Radiation Source:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 156 Rads(Si)/sec. The total dose schedule can be found in Table I.

### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were biased during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

## V. <u>Summary</u>:

Based on the test data recorded during radiation testing, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID.

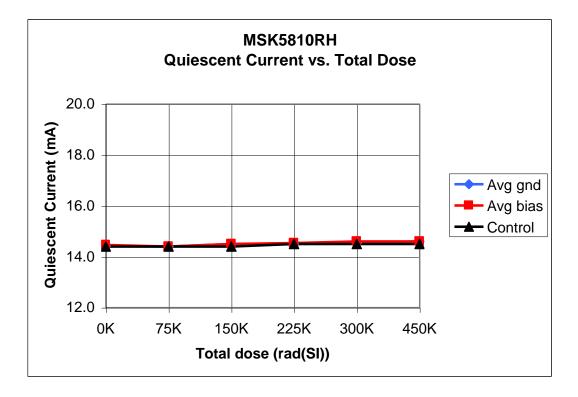
Dosimetry Equipment	
Bruker Biospin # 0141	

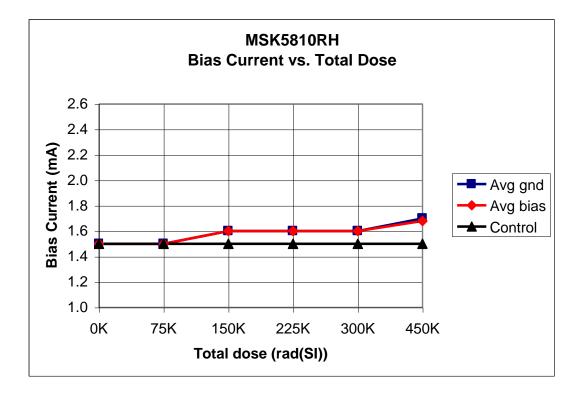
Irradiation Date	
11/06/09	

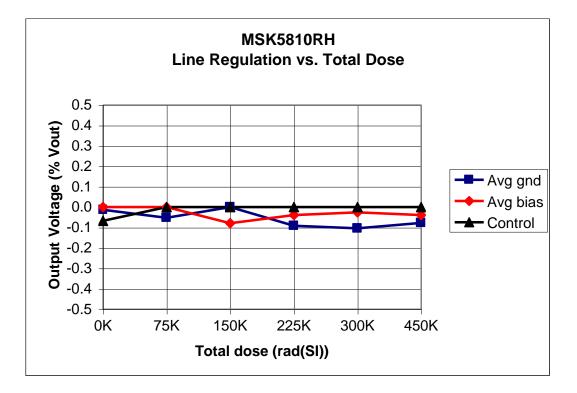
Incremental Dose rads(Si)	Cumulative Dose rads(Si)
77,376	77,376
77,376	154,752
77,376	232,128
77,376	309,504
154,752	464,256
	Dose rads(Si) 77,376 77,376 77,376 77,376

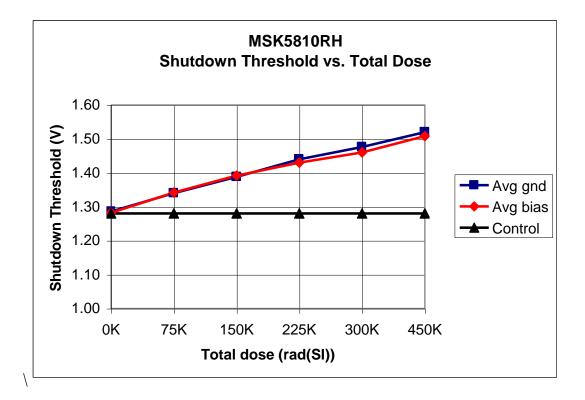
Unbiased S/N - 0320, 0321, 0322, 0324, 0	325
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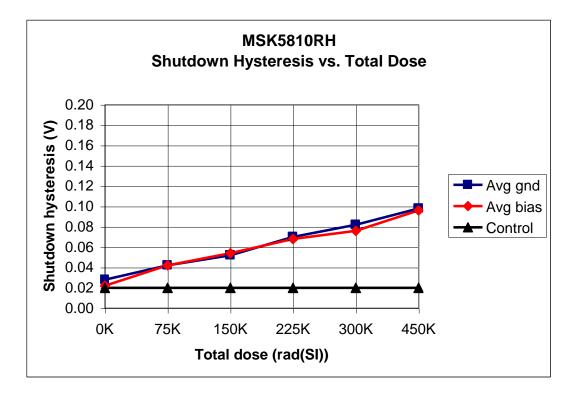
Table 1

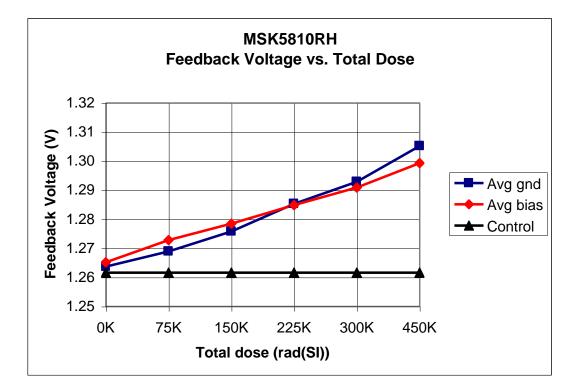


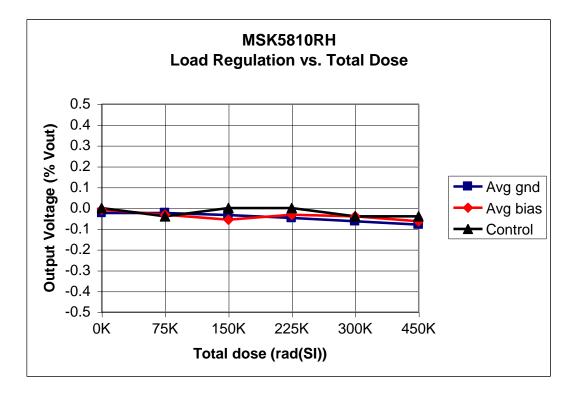


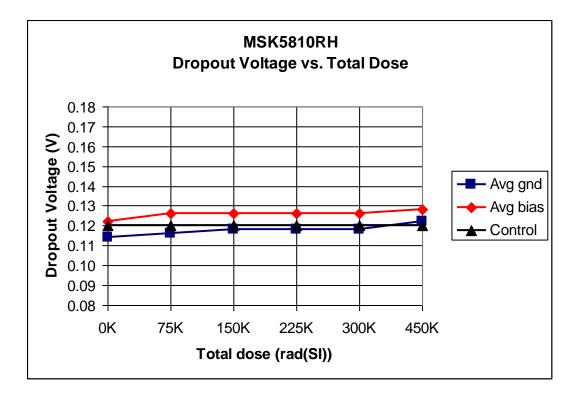


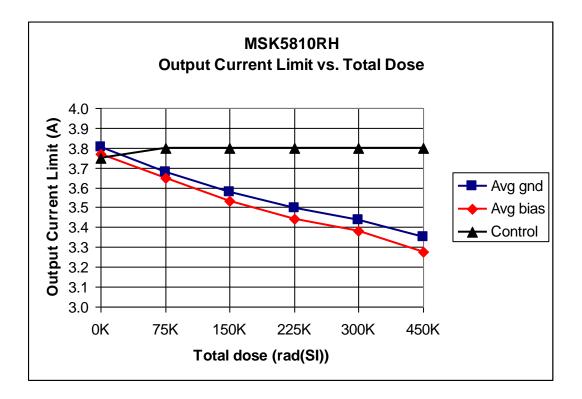












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (First Test) Updated on December 24, 2008 March 26, 2009 (Second Test) September 3, 2009 (Third Test)

> M. Bilecki B. Erwin

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK5800RH, MSK 5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and MSK5827RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

### II. <u>Radiation Source</u>:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 172 Rads(Si)/sec. The total dose schedule can be found in Table I.

### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were kept under bias during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

## V. <u>Summary</u>:

Based on the test data recorded during radiation testing, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID.

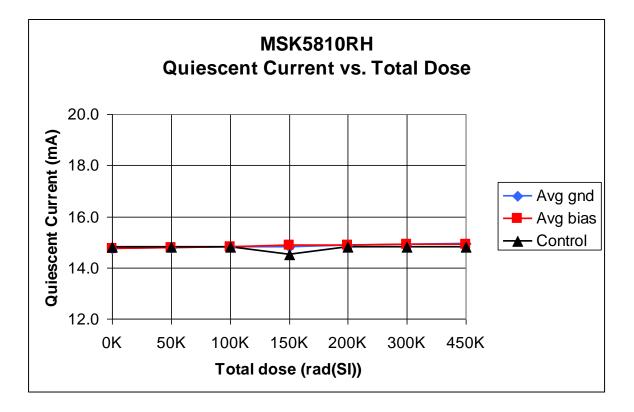
Dosime	try Equipment
Bruker E	Biospin # 0141

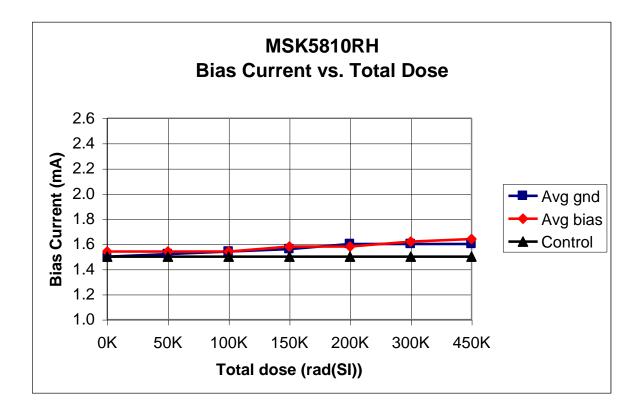
Irradiation Date	
09/03/09	

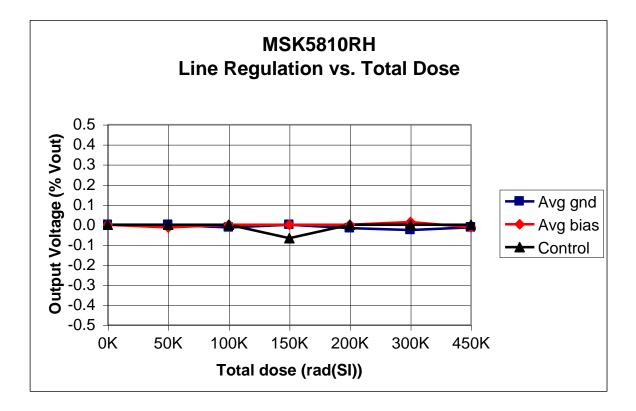
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
5:00	51,600	51,600
5:00	51,600	103,200
5:00	51,600	154,800
5:00	51,600	206,400
9:59	103,028	309,428
14:58	154,456	463,884

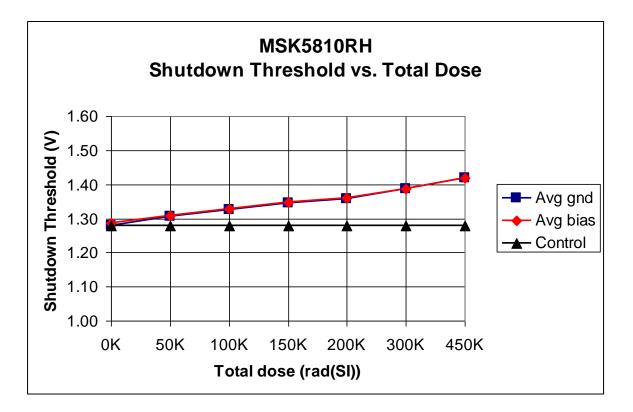
Unbiased S/N – 0281, 0282, 0283, 0284, 0285

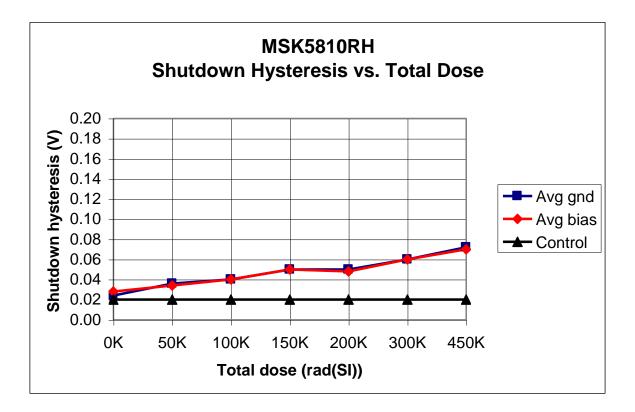
### Table 1

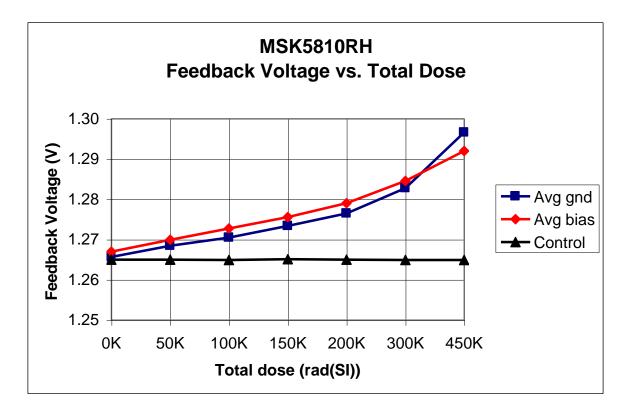


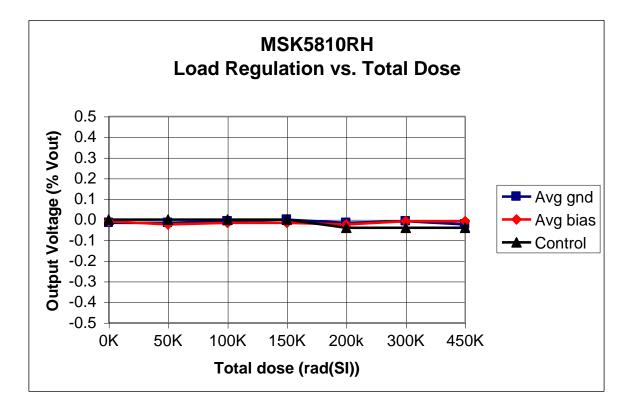


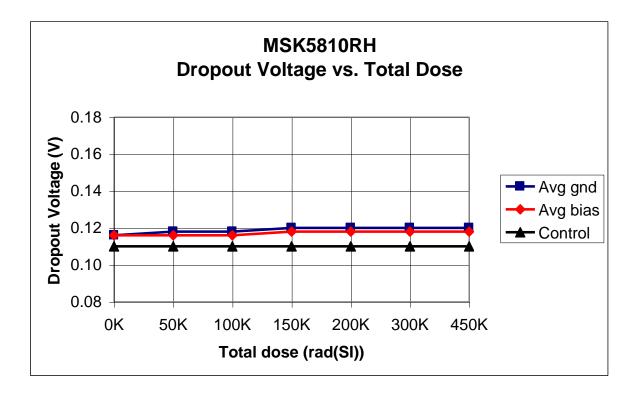


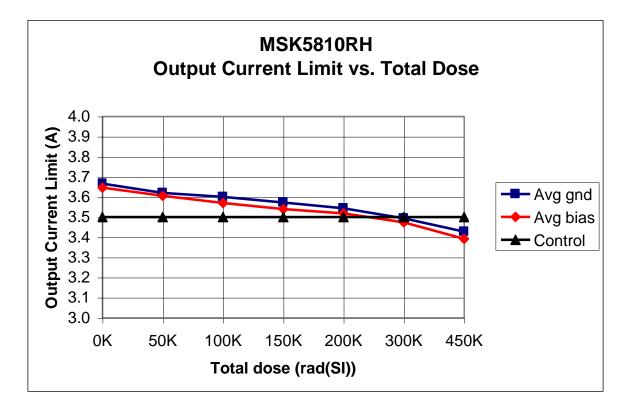












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (First Test) Updated on December 24, 2008 March 26, 2009 (Second Test)

> M. Bilecki P. Musil

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and the MSK5800RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

## II. Radiation Source:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 184 Rads(Si)/sec. The total dose schedule can be found in Table I.

### III. <u>Test Setup</u>:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were kept under bias during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

## V. <u>Summary</u>:

Based on the test data recorded during radiation testing and statistical analysis, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID.

Dosimetry Equipment Bruker Biospin # 0141

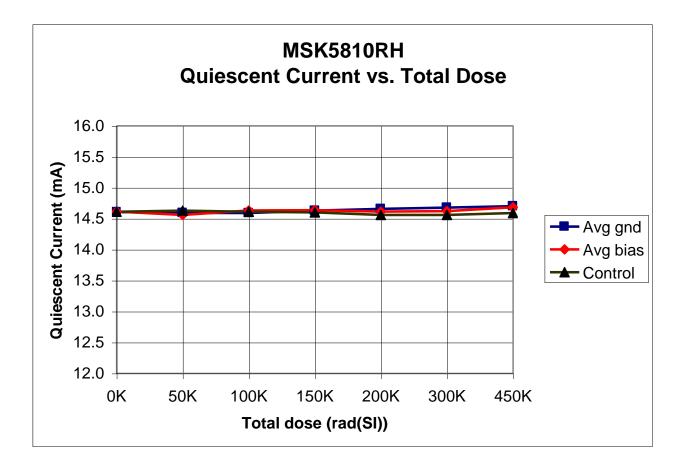
Irradiation Date	
03/17/09	

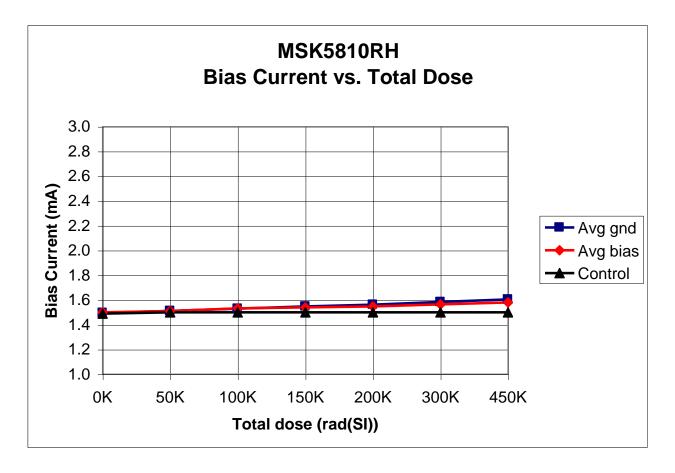
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)
4:40	51,520	51,520
4:40	51,520	103,040
4:40	51,520	154,560
4:40	51,520	206,080
9:20	103,040	309,120
14:00	154,560	463,680

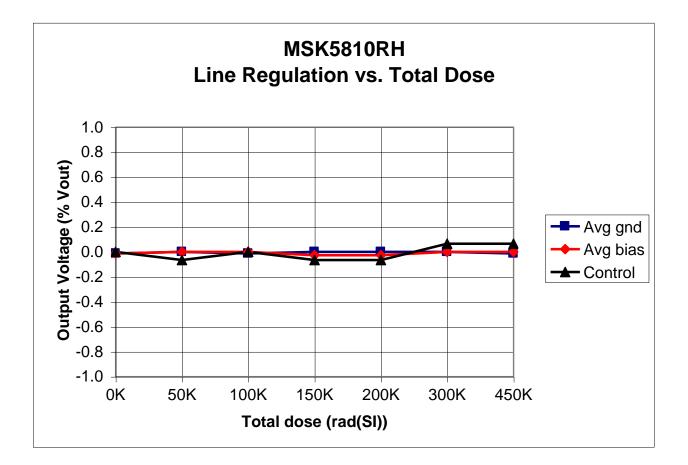
Biased S/N – 0054, 0055, 0056, 0057, 0058

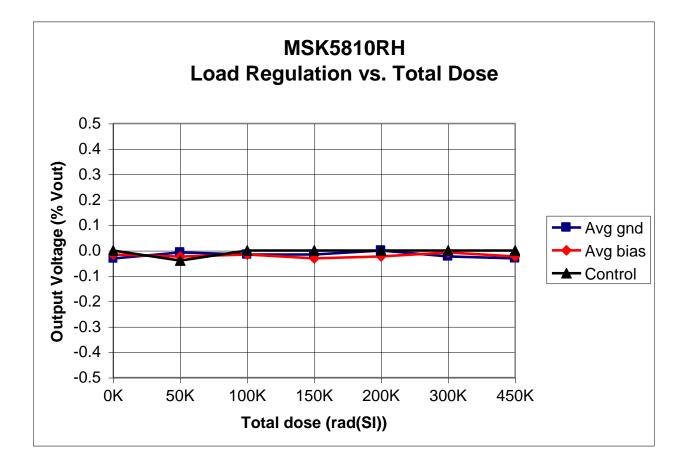
Unbiased S/N – 0059, 0060, 0061, 0062, 0063

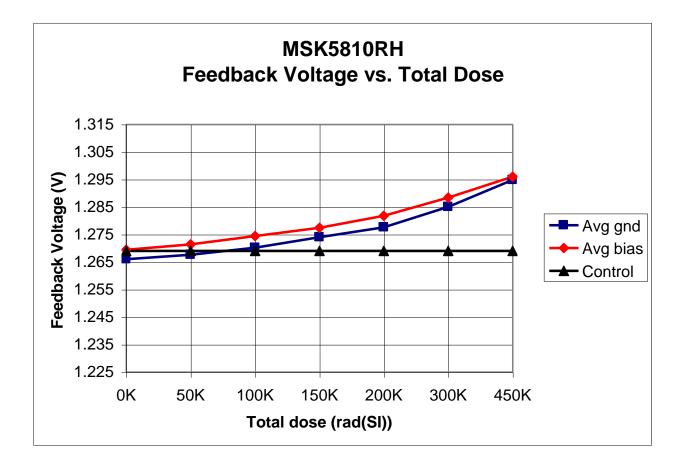
### Table 1

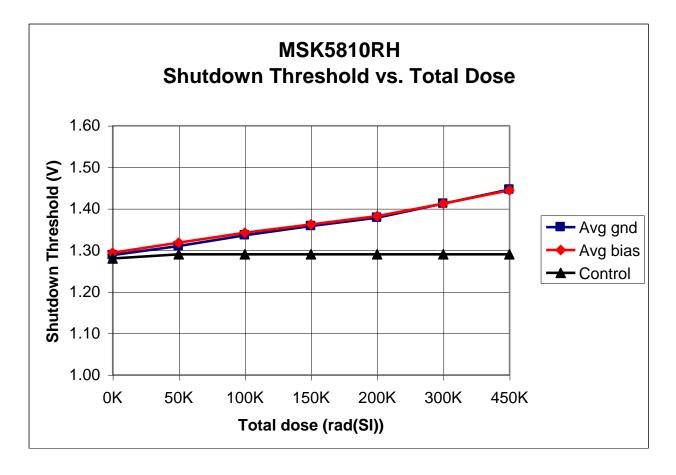


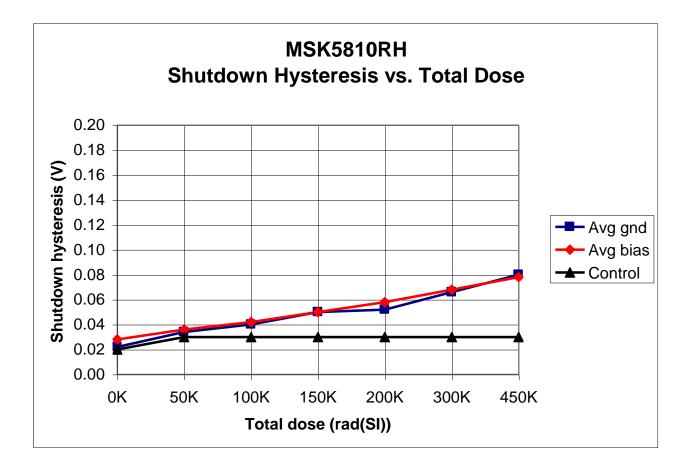


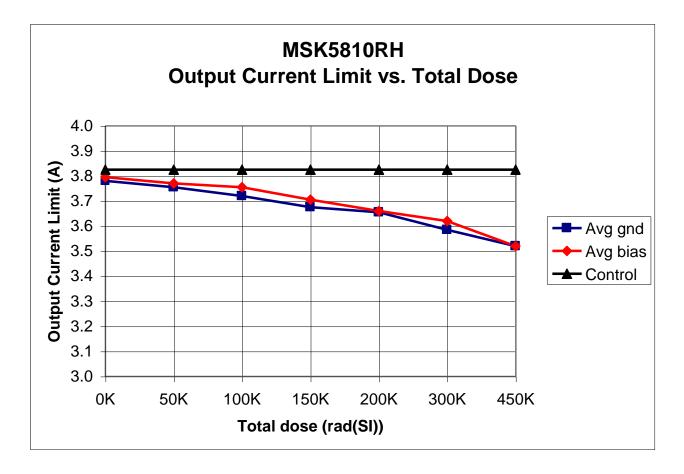


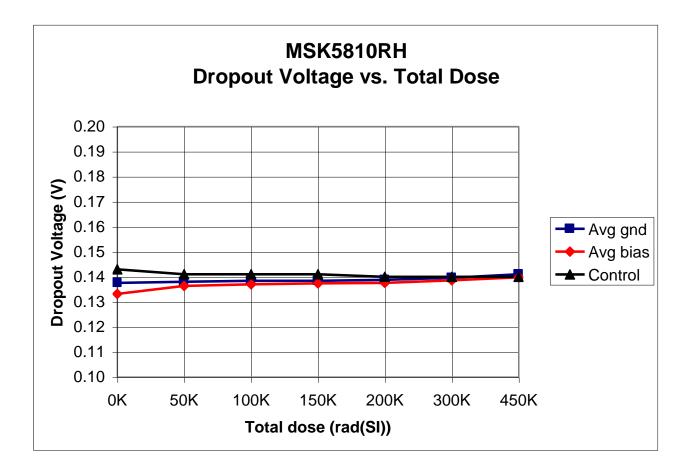












# **MSK 5822 RH**

# RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

March 21, 2009

J. Douglas P. Musil

The total dose radiation test plan for the MSK 5822 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5822 RH.

### II. Radiation Source:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 179 Rads(Si)/sec. The total dose schedule can be found in Table I.

### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were kept under bias during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. Data:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

## V. <u>Summary</u>:

Based on the test data recorded during radiation testing, the MSK5822RH qualified as a 300 KRAD (Si) radiation hardened device. Output Voltage, Output Current Limit and Drop Out Voltage exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID.

Dosimetry Equipment

Bruker Biospin # 0141

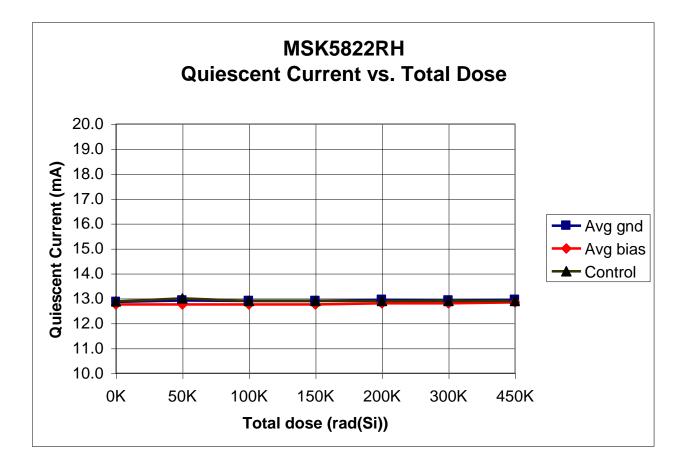
Irradiation Date	
03/17/09	

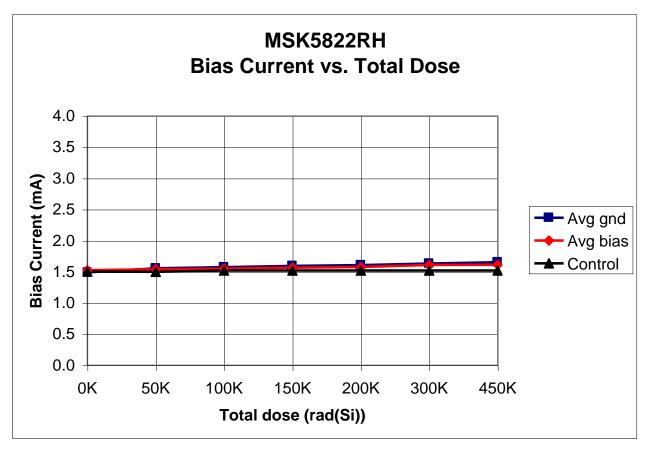
Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)	
4:48	51,552	51,552	
4:48	51,552	103,104	
4:48	51,552	154,656	
4:48	51,552	206,208	
9:36	103,104	309,312	
14:22	154,298	463,610	

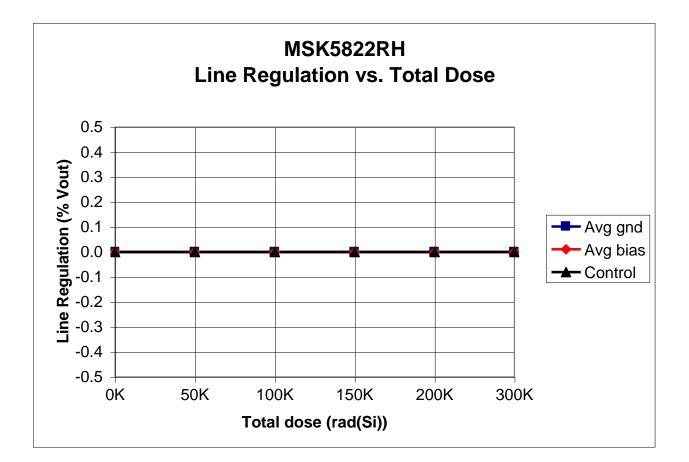
Biased S/N – 5874,5875,5876,5877,5878

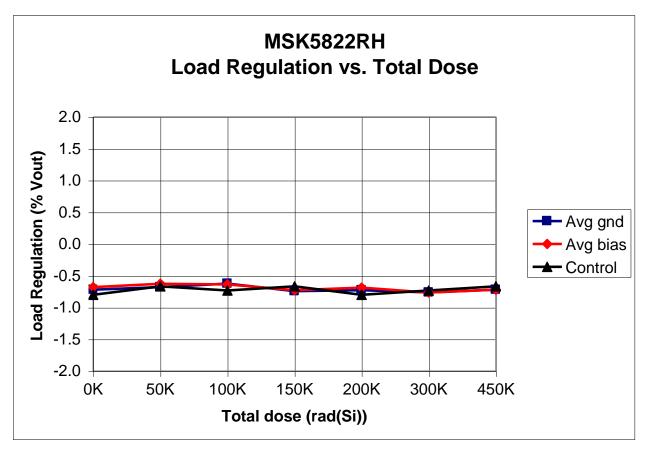
Unbiased S/N - 5879,5880,5881,5883,5885

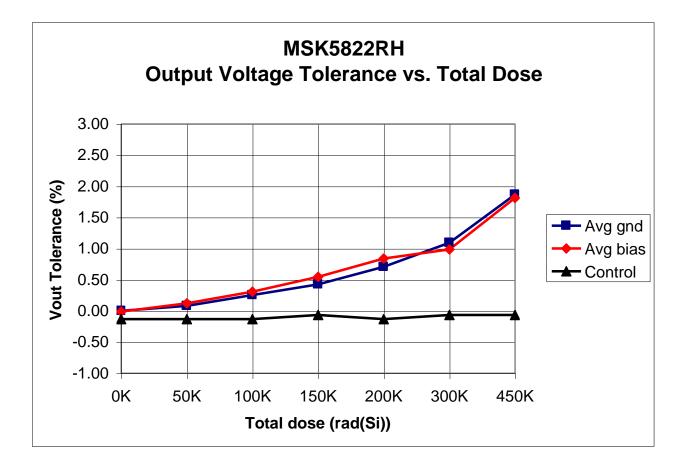
#### Table 1

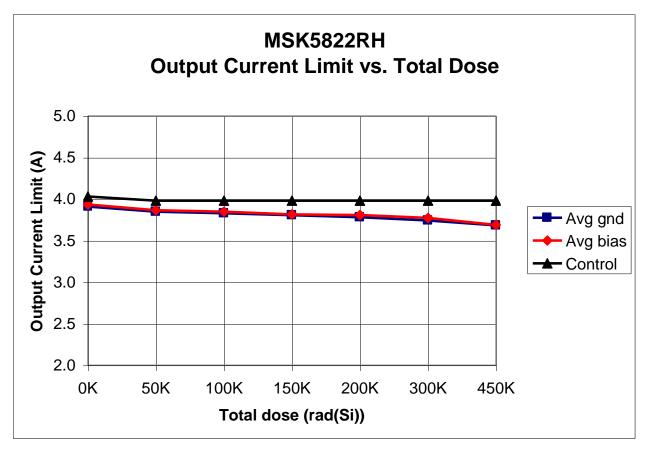


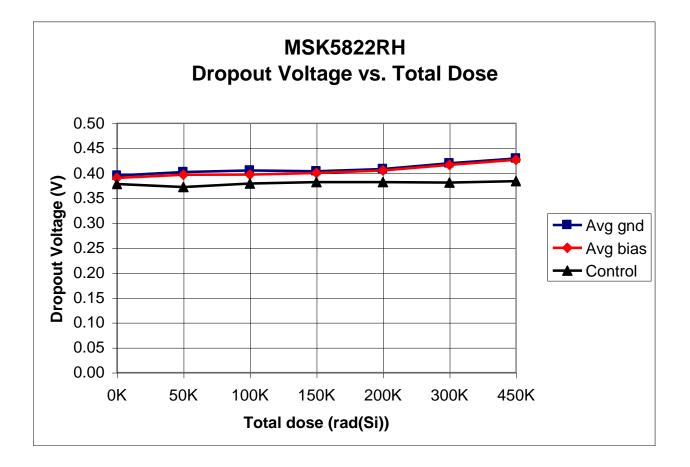












# MSK 5810 RH (MSK5800RH, MSK5820RH, MSK5821RH, MSK5822RH) RAD Hard Ultra Low Dropout Adjustable Positive Linear Regulator

November 25, 2008 (First Test) Updated on December 24, 2008 March 26, 2009 (Second Test)

> M. Bilecki P. Musil

The total dose radiation test plan for the MSK 5810 RH series was developed to qualify the devices as RAD Hard to 300 KRAD (Si). The testing was performed beyond 300 KRAD (Si) to show trends in device performance as a function of total dose. The test does not classify maximum radiation tolerance of the device, but simply offers designers insight to the critical parameter-shifts up to the specified total dose level. The MSK5810RH, MSK5820RH, MSK5821RH, MSK5822RH, and the MSK5800RH all use the same active components. The data in this report is from direct measurement of the MSK5810RH response to irradiation but it is indicative of the response of all five device types and is applicable to all five types.

MIL-STD-883 Method 1019.7 and ASTM F1892-06 were used as guidelines in the development and implementation of the total dose test plan for the MSK 5810RH.

## II. Radiation Source:

Total dose was performed at the University of Massachusetts, Lowell, using a cobalt 60 radiation source. The dose rate was determined to be 184 Rads(Si)/sec. The total dose schedule can be found in Table I.

### III. Test Setup:

All test samples were subjected to Group A Electrical Test at 25°C in accordance with the device data sheet. In addition, all devices received 320 hours of burn-in per MIL-STD-883 Method 1015. For test platform verification, one control device was tested at 25°C. Ten devices were then tested at 25°C, prior to irradiation, and were found to be within acceptable test limits.

The devices were vertically aligned with the radiation source and enclosed in a lead/aluminum container during irradiation. Five devices were kept under bias during irradiation. Maximum recommended operating voltage of +7.5V was used for the bias condition. Five devices had all leads grounded during irradiation for the unbiased condition.

After each irradiation the device leads were shorted together and transported to the MSK automatic electrical test platform and tested IAW MSK device data sheet. Testing was performed on irradiated devices, as well as the control device, at each total dose level. Electrical tests were completed within one hour of irradiation. Devices were subjected to subsequent radiation doses within two hours of removal from the radiation field.

#### IV. <u>Data</u>:

All performance curves are averaged from the test results of the biased and unbiased devices, respectively. If required, full test data can be obtained by contacting M.S. Kennedy Corporation.

## V. <u>Summary</u>:

Based on the test data recorded during radiation testing and statistical analysis, the MSK5810RH qualified as a 300 KRAD (Si) radiation hardened device. Feedback Voltage, Shutdown Threshold, and Output Current Limit exhibited the most significant shift due to irradiation, however all performance curves stayed within specification up to 450 KRAD (Si) TID.

> Dosimetry Equipment Bruker Biospin # 0141

Irradiation Date
03/17/09

Exposure Length (min:sec)	Incremental Dose rads(Si)	Cumulative Dose rads(Si)	
4:40	51,520	51,520	
4:40	51,520	103,040	
4:40	51,520	154,560	
4:40	51,520	206,080	
9:20	103,040	309,120	
14:00	154,560	463,680	

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Biased S/N –	0054.	0055.	0056.	0057.	0058

#### Table 1

